

**2020 Spring**

# ***Advanced Solidification***

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# Binary phase diagrams

Contents for previous class  
Solid-Liquid Equilibrium in Alloys

## 1) Simple Phase Diagrams

Both are ideal soln. → At T change, curvature and width change of G curve by S

## 2) Systems with miscibility gap $\Delta H_{mix}^L = 0$ $\Delta H_{mix}^S > 0$

At T change, curvature and width change of G curve by S + shape change of curve by H

## 4) Simple Eutectic Systems $\Delta H_{mix}^L = 0$ $\Delta H_{mix}^S \gg 0$

→ miscibility gap extends to the melting temperature.

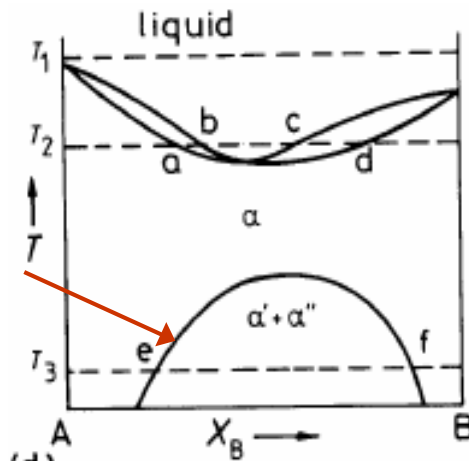
## 3) Ordered Alloys $\Delta H_{mix}^L = 0$ $\Delta H_{mix}^S < 0$

$\Delta H_{mix} < 0$  → A atoms and B atoms like each other. → Ordered alloy at low T

$\Delta H_{mix} \ll 0$  → The ordered state can extend to the melting temperature.

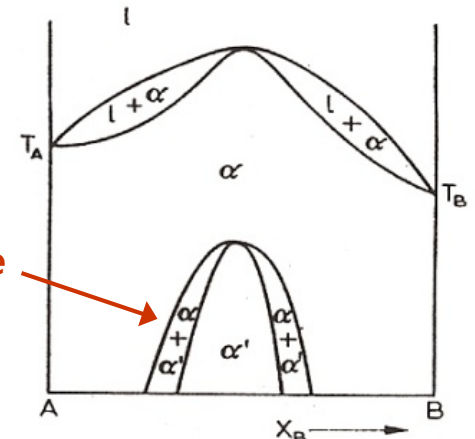
$$\Delta H_{mix}^{\alpha} > \Delta H_{mix}^l > 0$$

miscibility gap



$$\Delta H_{mix}^{\alpha} < \Delta H_{mix}^l < 0$$

Ordered phase



## Considerable difference between the melting points

### Eutectic reaction

$$\Delta H_{mix}^{\alpha} > \Delta H_{mix}^l > 0$$

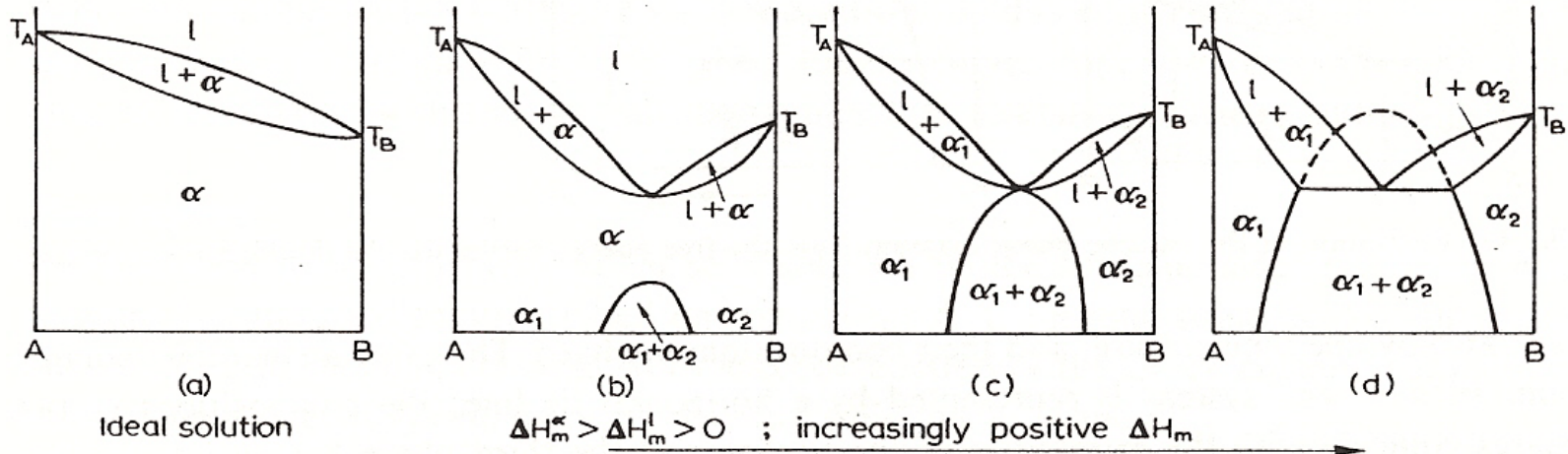


Fig. 43. Effect of increasingly positive departure from ideality in changing the phase diagram for a continuous series of solutions to a eutectic-type.

### Peritectic reaction

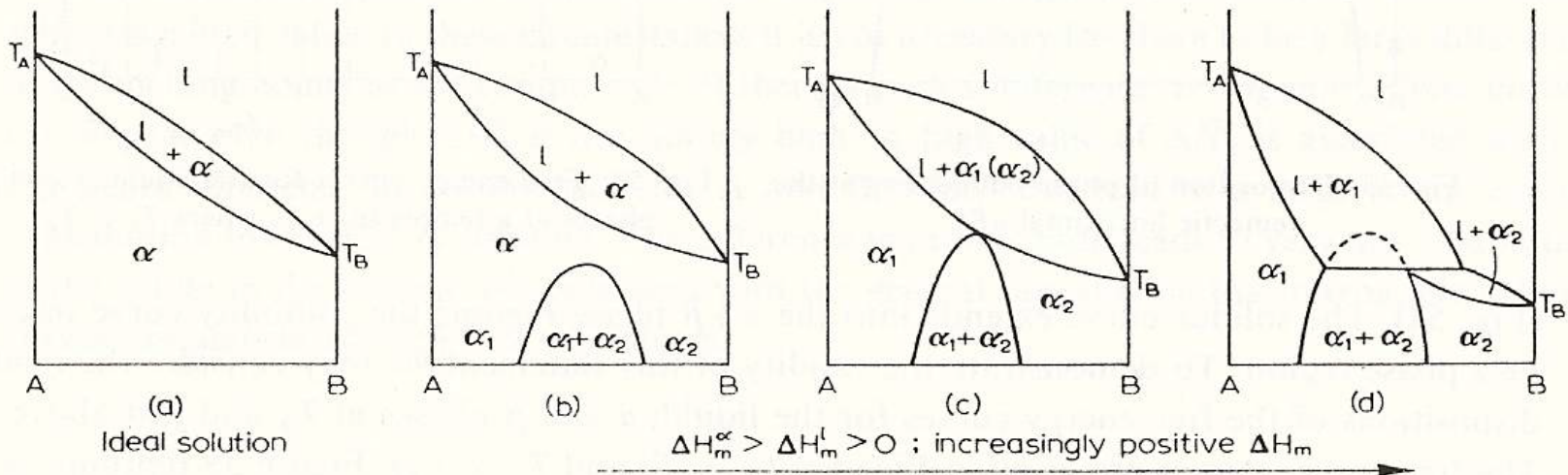


Fig. 61. Effect of increasingly positive departure from ideality in changing the phase diagram from a continuous series of solutions to a peritectic-type.

# 1.5 Binary phase diagrams

## Intermediate Phase

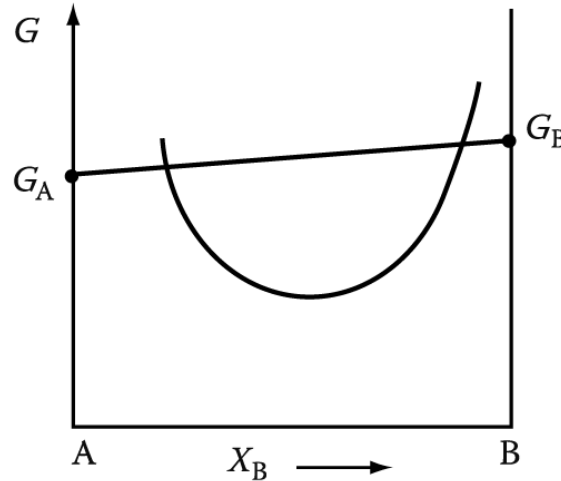
### \* Solid solution

- random mixing
- entropy ↑
- negative enthalpy ↓

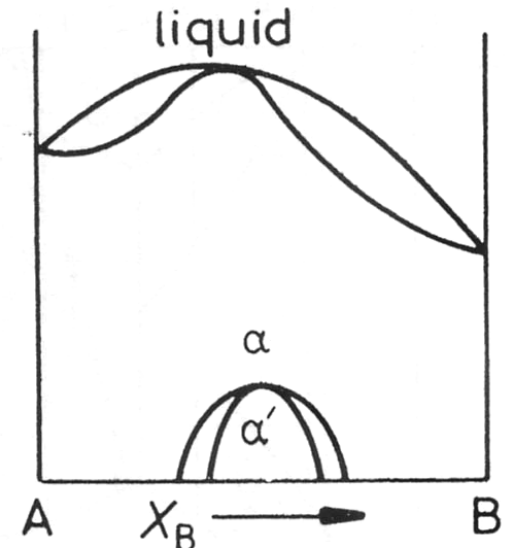
$$\Delta H_{mix}^S < 0$$

Wide compositional range

→ G ↓



(b)



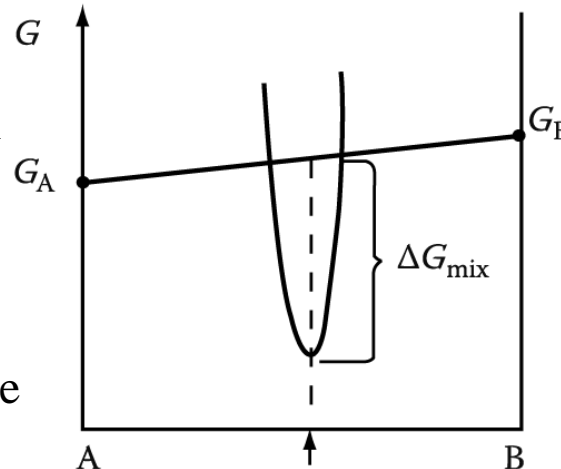
### \* Compound : AB, A<sub>2</sub>B...

- entropy ↓
- covalent, ionic contribution
- enthalpy more negative ↓

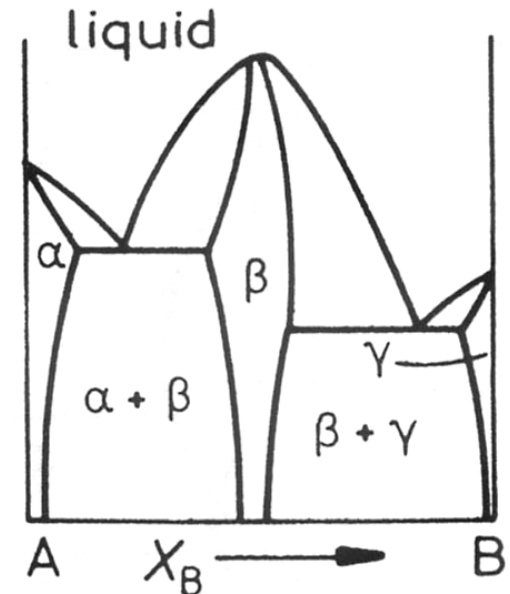
$$\Delta H_{mix}^S \ll 0$$

Narrow compositional range

→ G ↓



(a)



Microstructure is the collection of defects in the materials.

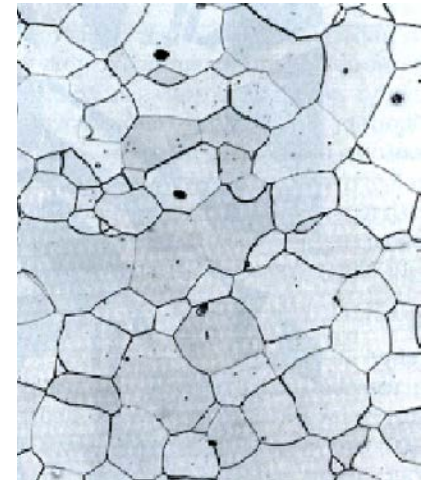
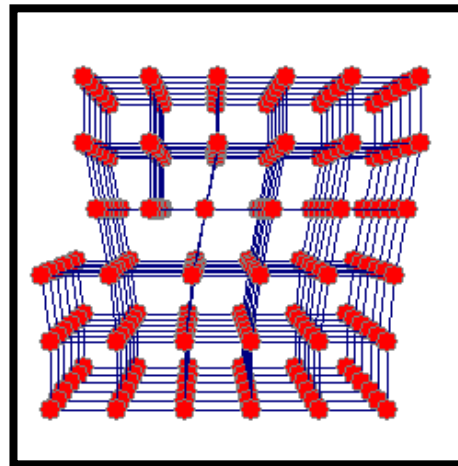
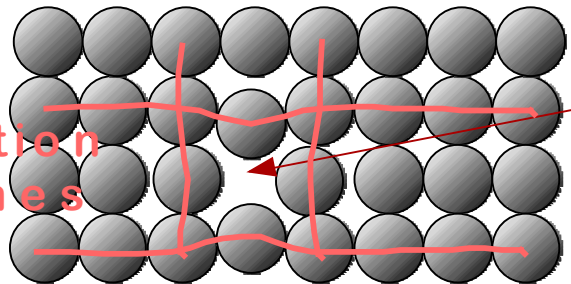
□ **Imperfection** in Metallic Materials ;

**Point defect** : Vacancies, interstitials, Impurities

**Line defect** : Dislocations, Cellular and lineage substructure

**Plane defect** : Grain Boundaries, Free Surfaces

**Bulk defect** : Voids, Cracks



# *Heterogeneous Nucleation*

Heterogeneous nucleation must occur on some substrate:

grain boundaries

triple junctions

dislocations

(existing) second phase particles

Consider a grain boundary: why is it effective?

Answer: by forming on a grain boundary, an embryo can offset its “cost” in interfacial energy by **eliminating some grain boundary area.**

Equilibrium concentration  $X_V^e$  will be that which gives the minimum free energy.

at equilibrium  $\left(\frac{dG}{dX_V}\right)_{X_V=X_V^e} = 0$

$$\Delta H_V - T\Delta S_V + RT \ln X_V^e = 0$$

A constant ~3, independent of T

Rapidly increases with increasing T

$$X_V^e = \exp\left(\frac{\Delta S_V}{R}\right) \exp\left(\frac{-\Delta H_V}{RT}\right)$$

putting  $\Delta G_V = \Delta H_V - T\Delta S_V$

$$X_V^e = \exp\left(\frac{-\Delta G_V}{RT}\right)$$

- In practice,  $\Delta H_V$  is of the order of 1 eV per atom and  $X_V^e$  reaches a value of about  $10^{-4} \sim 10^{-3}$  at the melting point of the solid

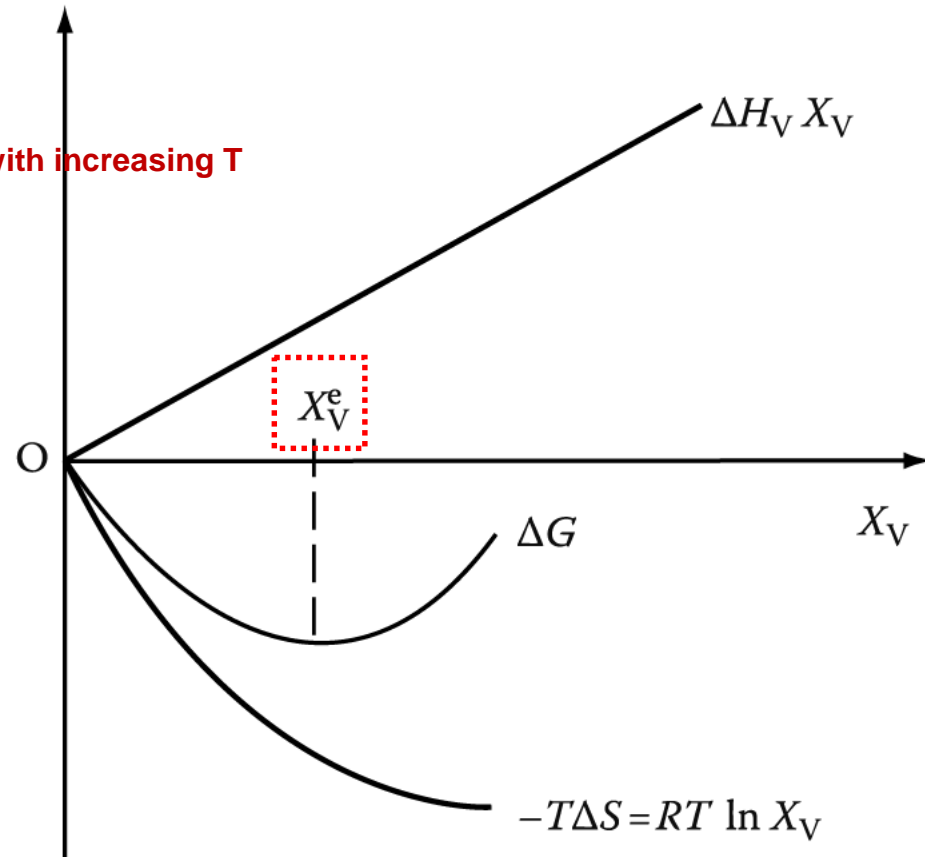


Fig. 1.37 Equilibrium vacancy concentration.

: adjust so as to reduce G to a minimum

## c) Quenched-in Vacancies

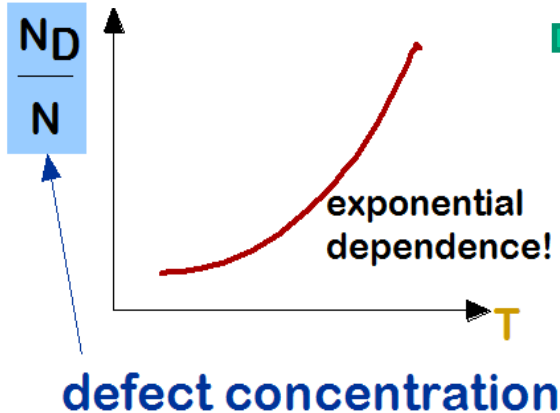
In the vicinity of grain boundaries on subsequent aging,

### Precipitate-Free Zone(PFZ) due to Vacancy Diffusion during quenching

Solute concentration within the zone ~ largely unchanged, but no precipitate at GB  
 $\therefore$  a critical vacancy supersaturation must be exceeded for nucleation to occur.

$$X_v^e = \exp \frac{-\Delta G_v}{RT}$$

$T \uparrow \rightarrow X_v^e \uparrow$



Similar PFZs can also form at inclusions and dislocations.

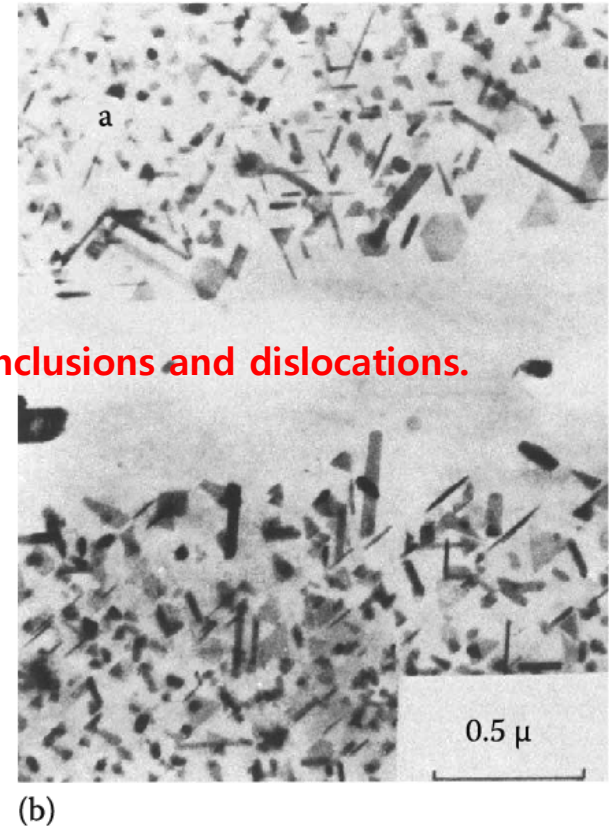
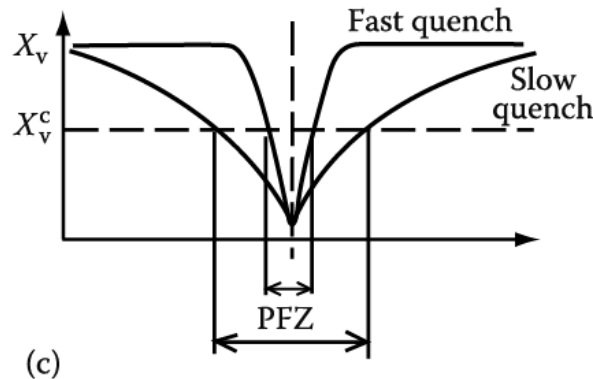
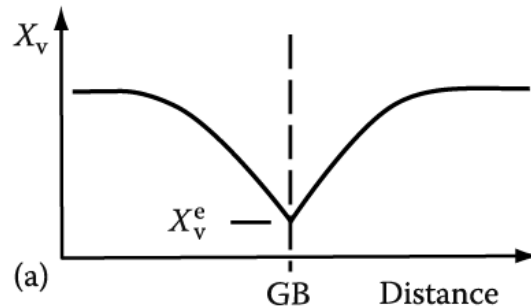


Fig. 5.35 A PFZ due to vacancy diffusion to a grain boundary during quenching.  
 (a) Vacancy concentration profile. (b) A PFZ in an Al-Ge alloy (x 20,000)  
 (c) Dependence of PFZ width on critical vacancy concentration  $X_v^c$  and rate of quenching.



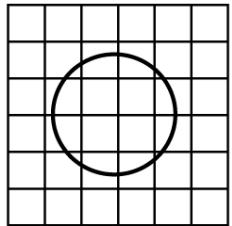
⑤ Stresses due to inclusions. (dislocation density ~ inclusion density)

# Coherency Loss

Precipitates with coherent interfaces = low interfacial E + coherency strain E

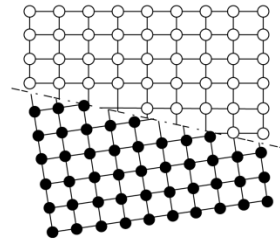
Precipitates with non-coherent interfaces = higher interfacial E

$$\Delta G(\text{coherent}) = 4\mu\delta^2 \cdot \frac{4}{3}\pi r^3 + 4\pi r^2 \cdot \gamma_{ch} \iff \Delta G(\text{non-coherent}) = 4\pi r^2 \cdot (\gamma_{ch} + \gamma_{st})$$



Coherency strain energy  
Eq. 3.39

Chemical interfacial E



Chemical and structural interfacial E

$$\frac{4}{3}\pi r^3 (4\pi\mu\delta^2) + 4\pi r^2 (\gamma_{ch}) = 4\pi r^2 (\gamma_{st} + \gamma_{ch})$$

coherent

$\Delta G_s$ -relaxed

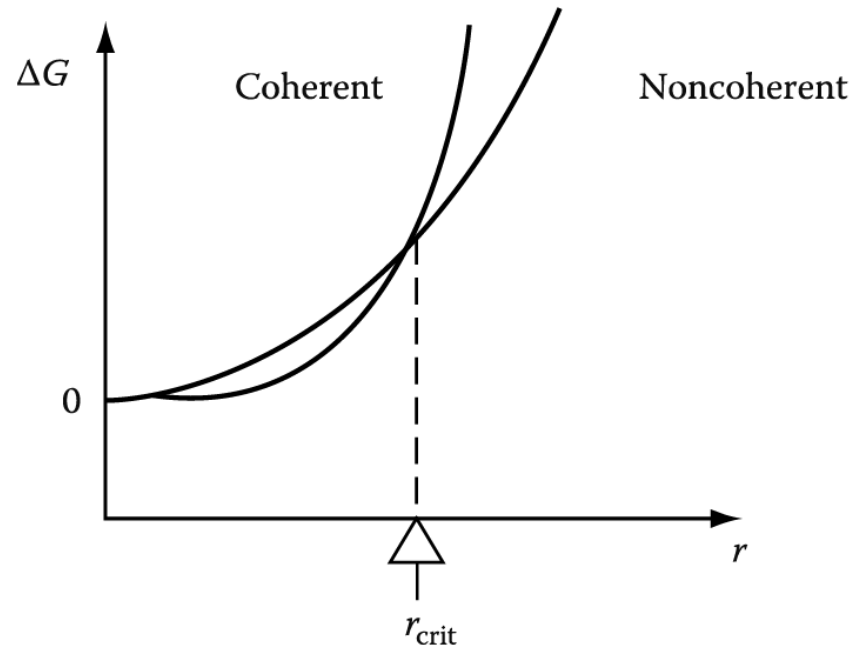
$$\therefore r_{crit} = \frac{3 \cdot \gamma_{st}}{4\mu\delta^2}$$

$$\approx \frac{1}{\delta}$$

( $\delta = (d_\beta - d_\alpha) / d_\alpha$  : misfit)

for small  $\delta$ ,  $\gamma_{st} \propto \delta$

(semicoherent interface)



⑥ Growth error: inherent feature

Fig. 3. 52 The total energy of matrix + precipitate vs. precipitate radius for spherical coherent and non-coherent (semicoherent or incoherent) precipitates.

# Liquid ↔ Solid transformation at $T_m$

Chapter 1: Equilibrium consideration (Thermodynamics)

Chapter 2: Atomic mechanism (Kinetics)

## Chapter 3. Nucleation

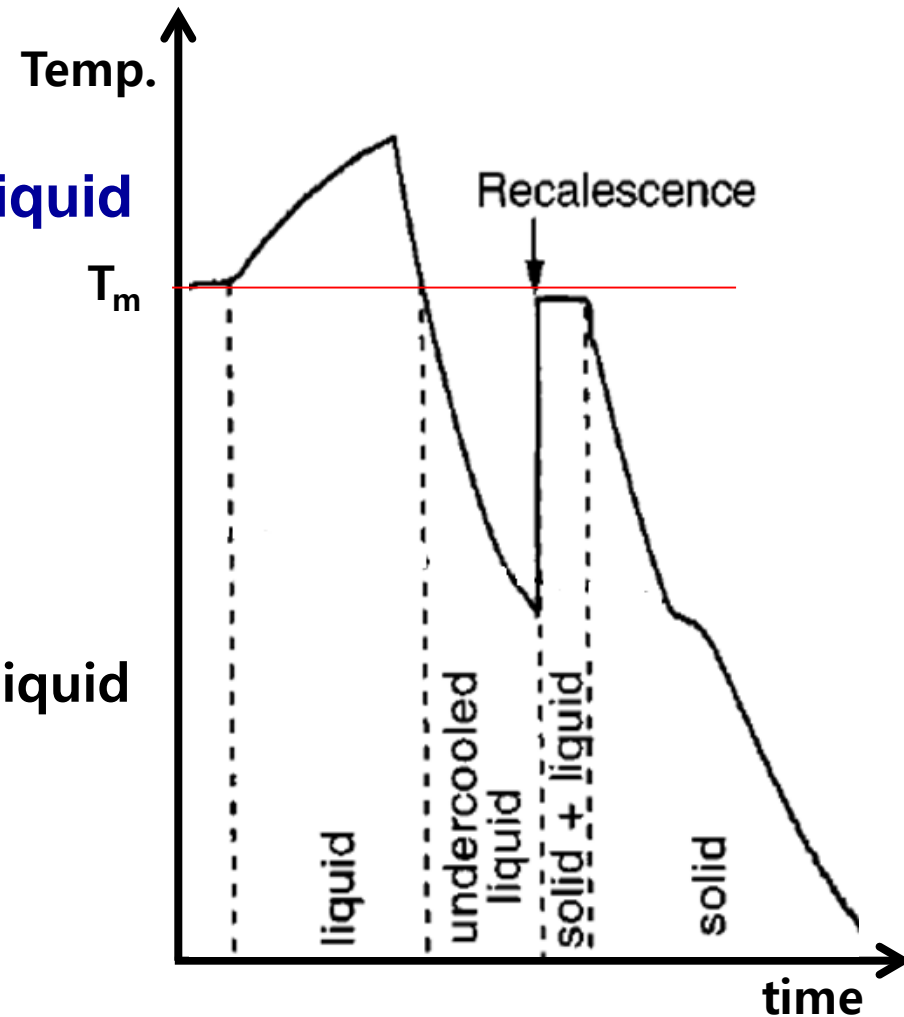
### 3.1. Metastability of Supercooled Liquid

**Solidification:**

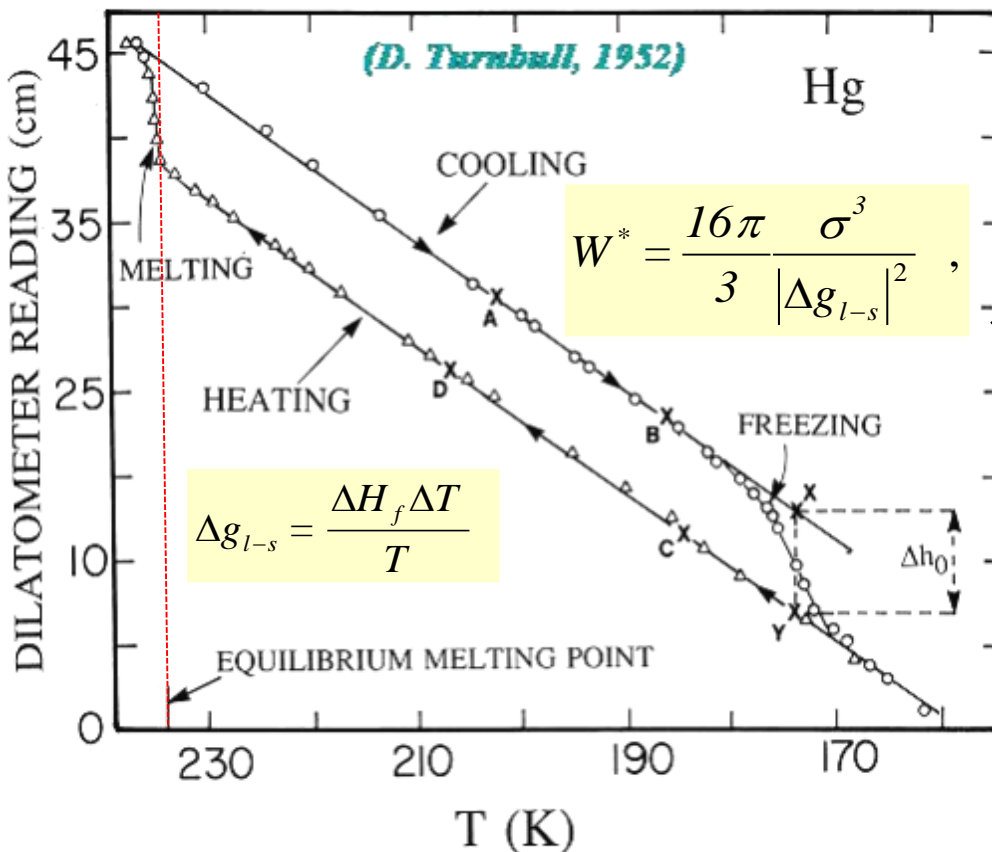
**Liquid** → **Solid**

Presence of metastable supercooled liquid

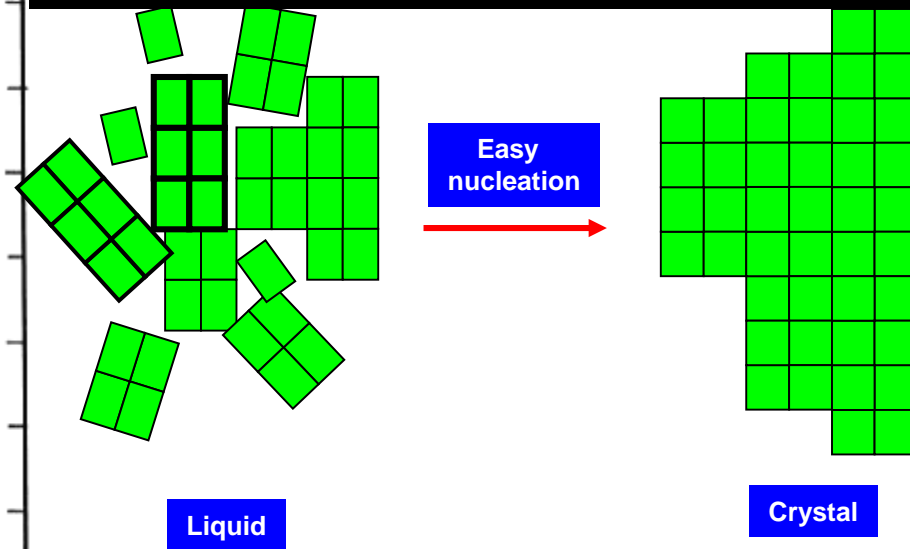
Why?



# Turnbull's Insight for Supercooling



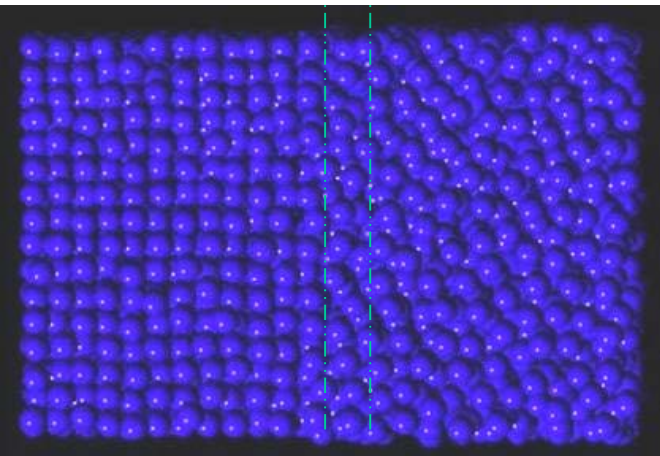
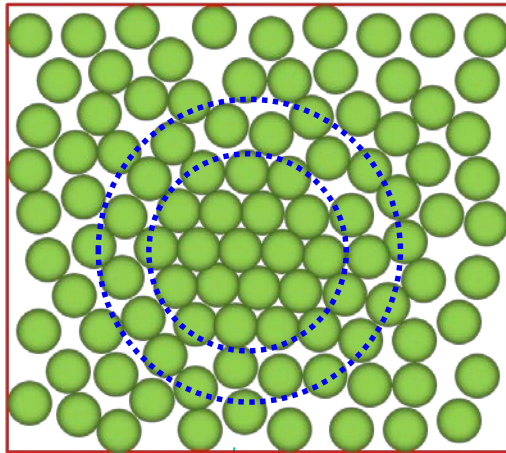
Microcrystalline structure for liquid metals  
 – Same short range order with crystals!



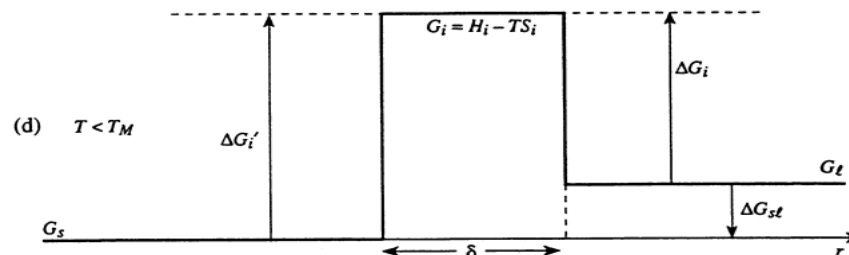
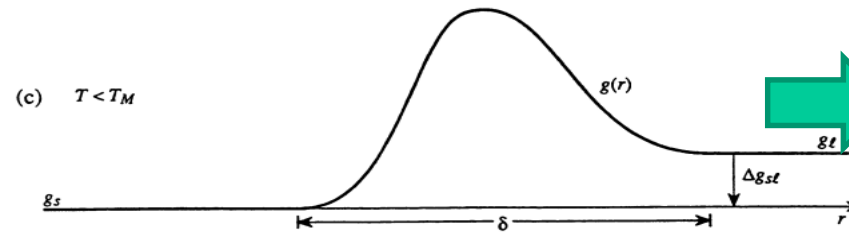
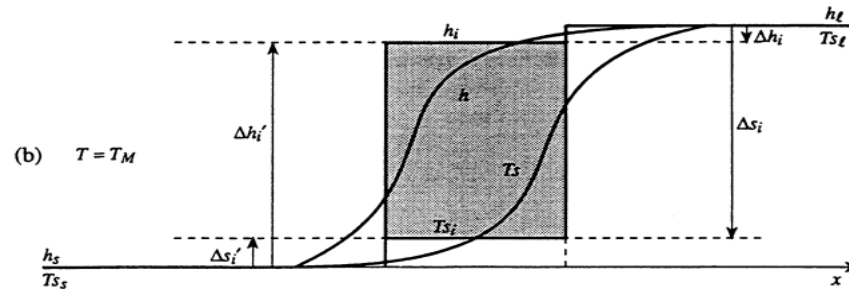
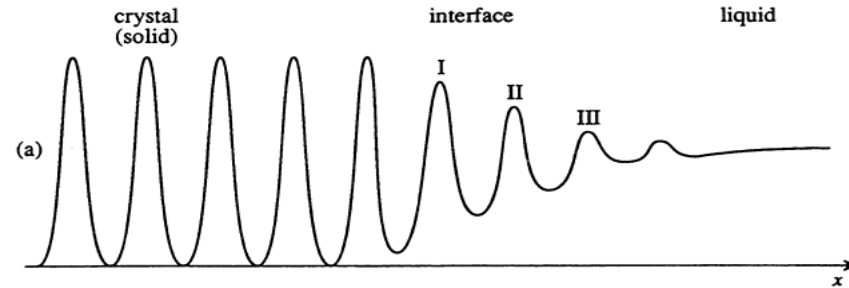
- ◆ How does the liquid metals resist on the crystallization?
- ◆ What is the origin of high nucleation barrier against the crystallization?
- What is the structure of interface between liquids and crystals?
- ◆ What is the **local order of liquid metals**?

# Turnbull's solid-liquid interface

Turnbull's insight : Liquid orders substantially near a crystal surface due to entropy decreasing caused by the crystal-melt interfacial tension

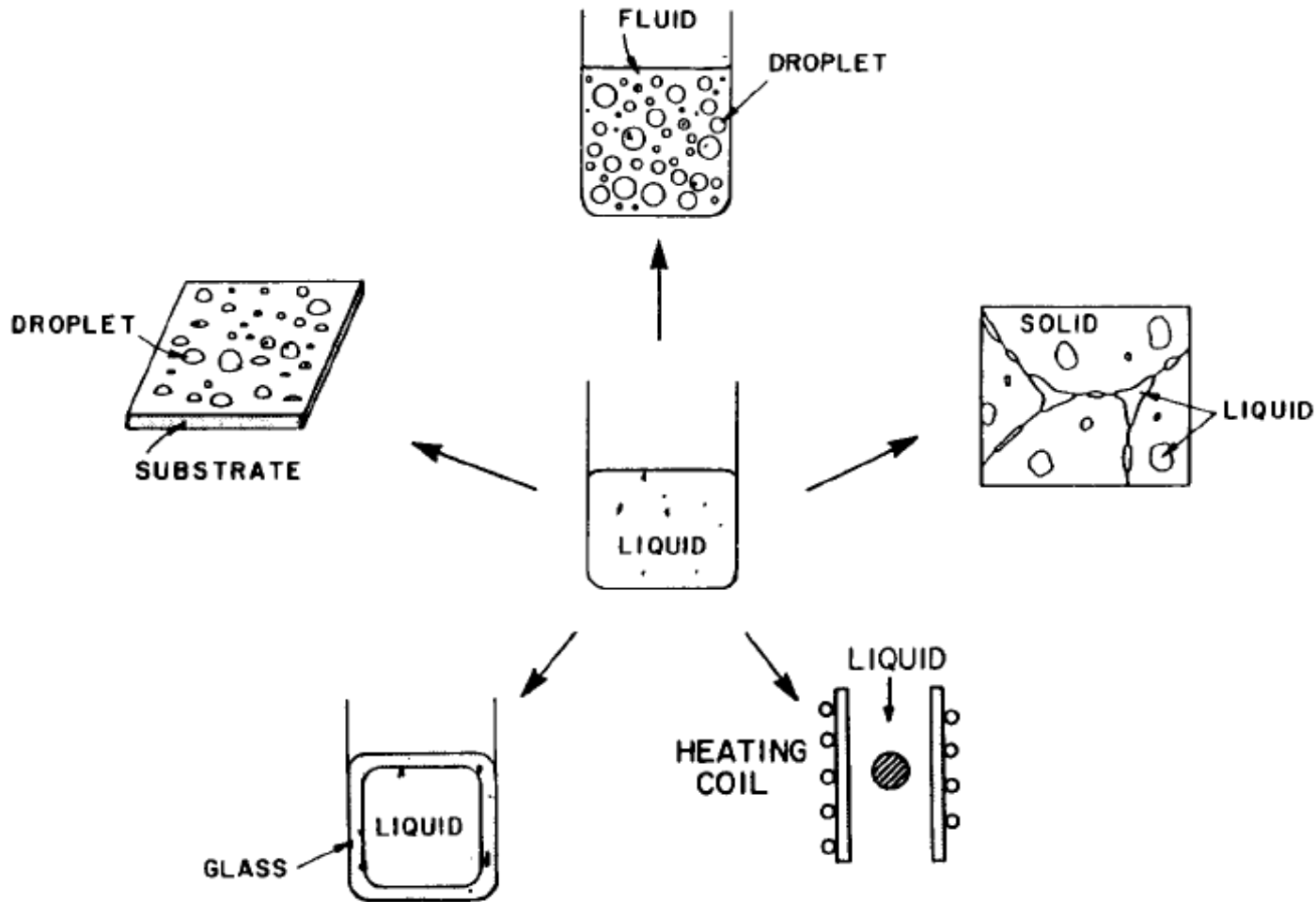


Solid state physics v47, 1 (1994)



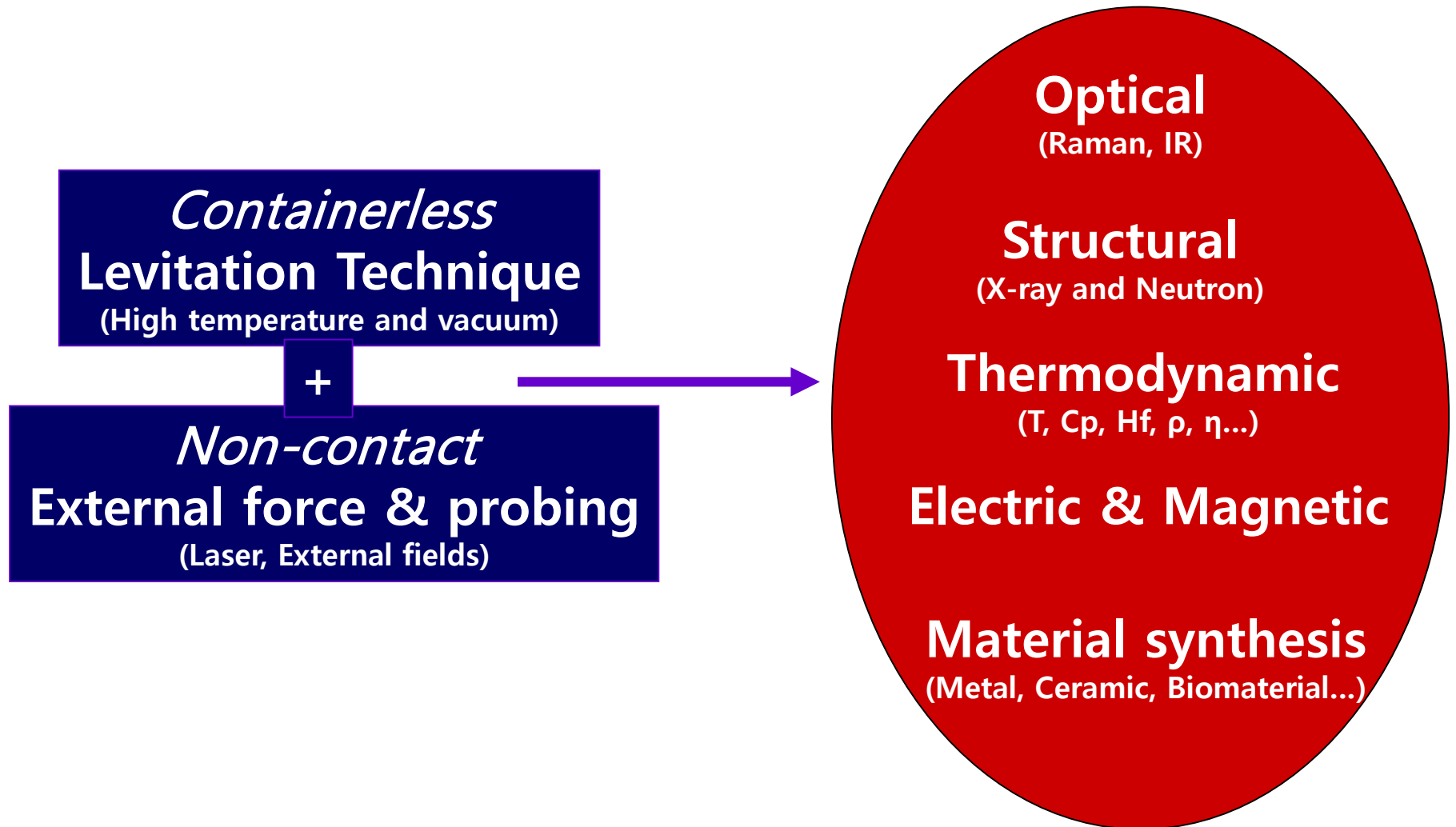
# How to Obtain Extensive Undercooling

John H. PEREPEZKO, MSE, 65 (1984) 125-135



By dispersing a liquid into a large number of small droplets within a suitable medium, the catalytic effects of active nucleants may be restricted to a small fraction of the droplets so that many droplets will exhibit extensive undercooling. 13

# Containerless and Contactless Measurement System

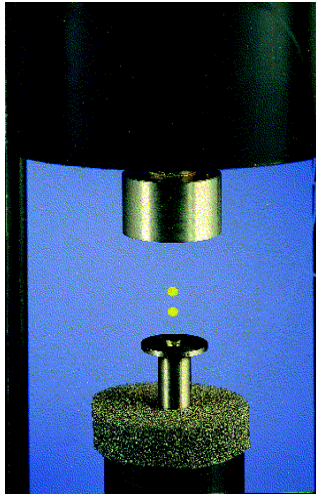
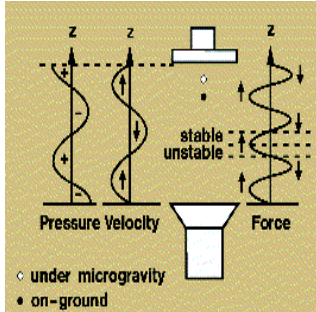


# High Temperature Levitation

Ultra-high temperature > 3000 °C

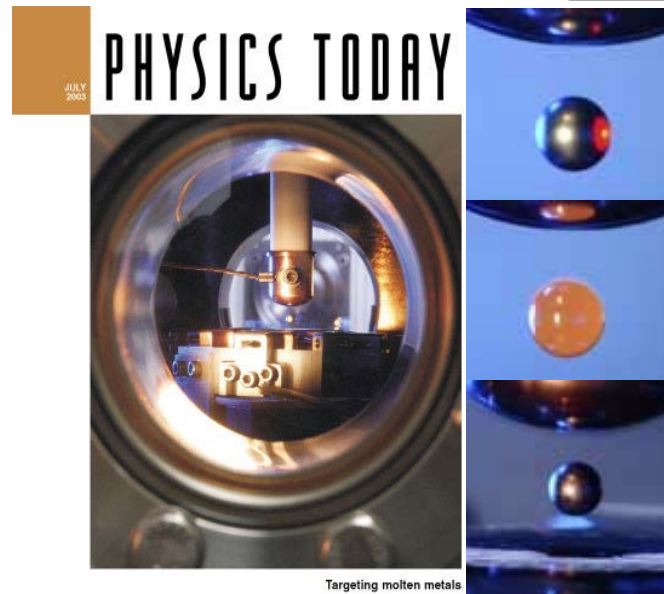
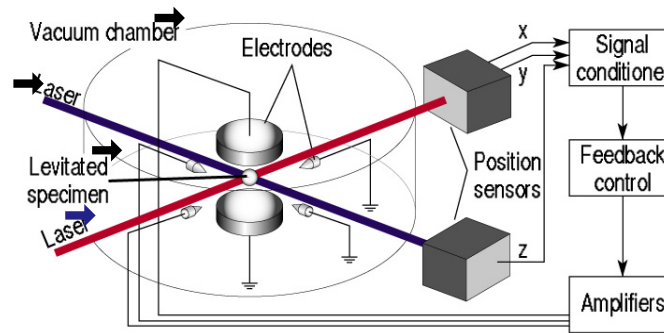
\* **Magnetic/diamagnetic/superconducting levitation** → Only magnetic sample, below  $T_c$

## Acoustic



Requirement of acoustic media, Unstable at high T

## Electrostatic



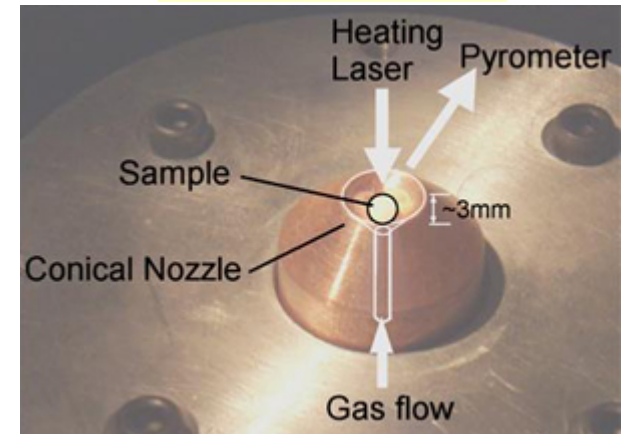
Physics Today, v56, p22, July 2003

All types of samples,  
Suitable for sample heating

## Electromagnetic



Only metallic & large mass sample  
**Aerodynamic**



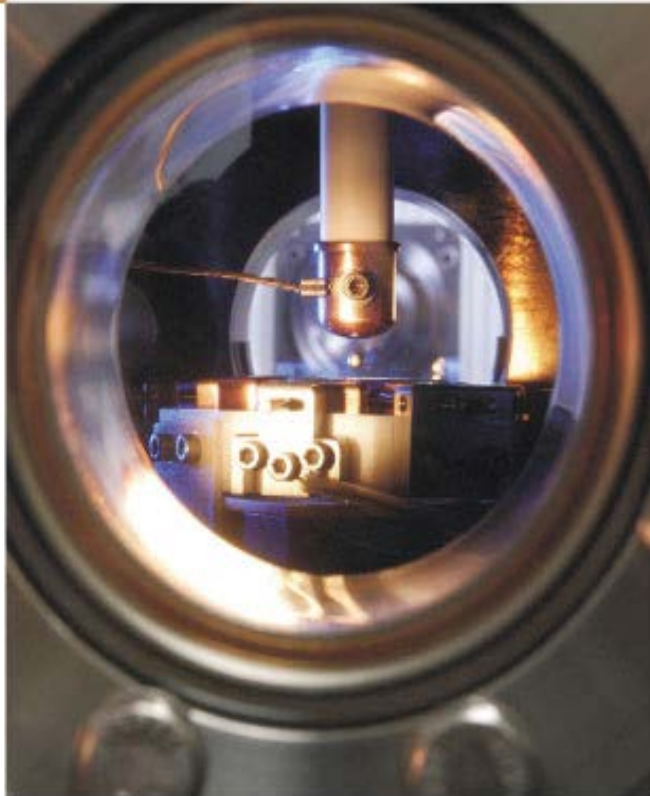
[http://ec.europa.eu/research/industrial\\_technologies/articles/article\\_2288\\_en.html](http://ec.europa.eu/research/industrial_technologies/articles/article_2288_en.html)

Difficult to control rotation of sample,  
Gas-sample reaction

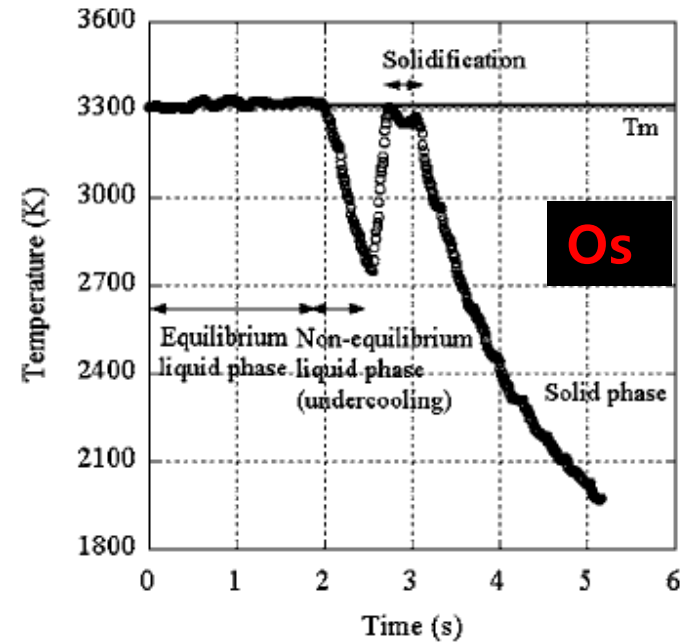
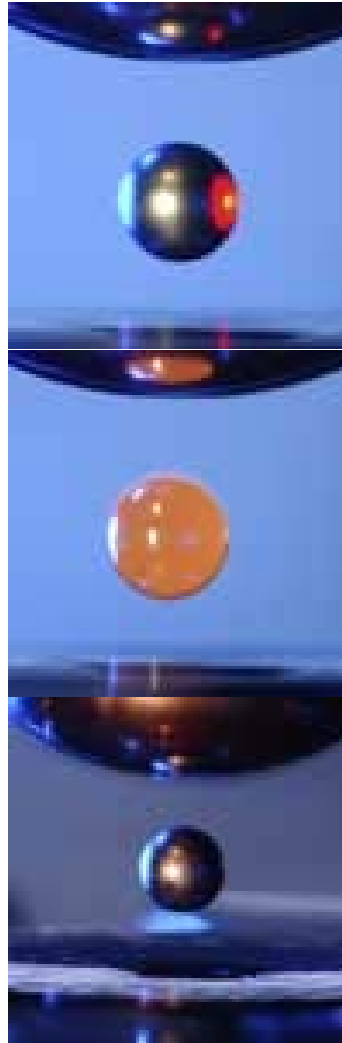
# Electrostatic Levitation (NASA, MSFC (Huntsville))

JULY  
2003

## PHYSICS TODAY



Targeting molten metals



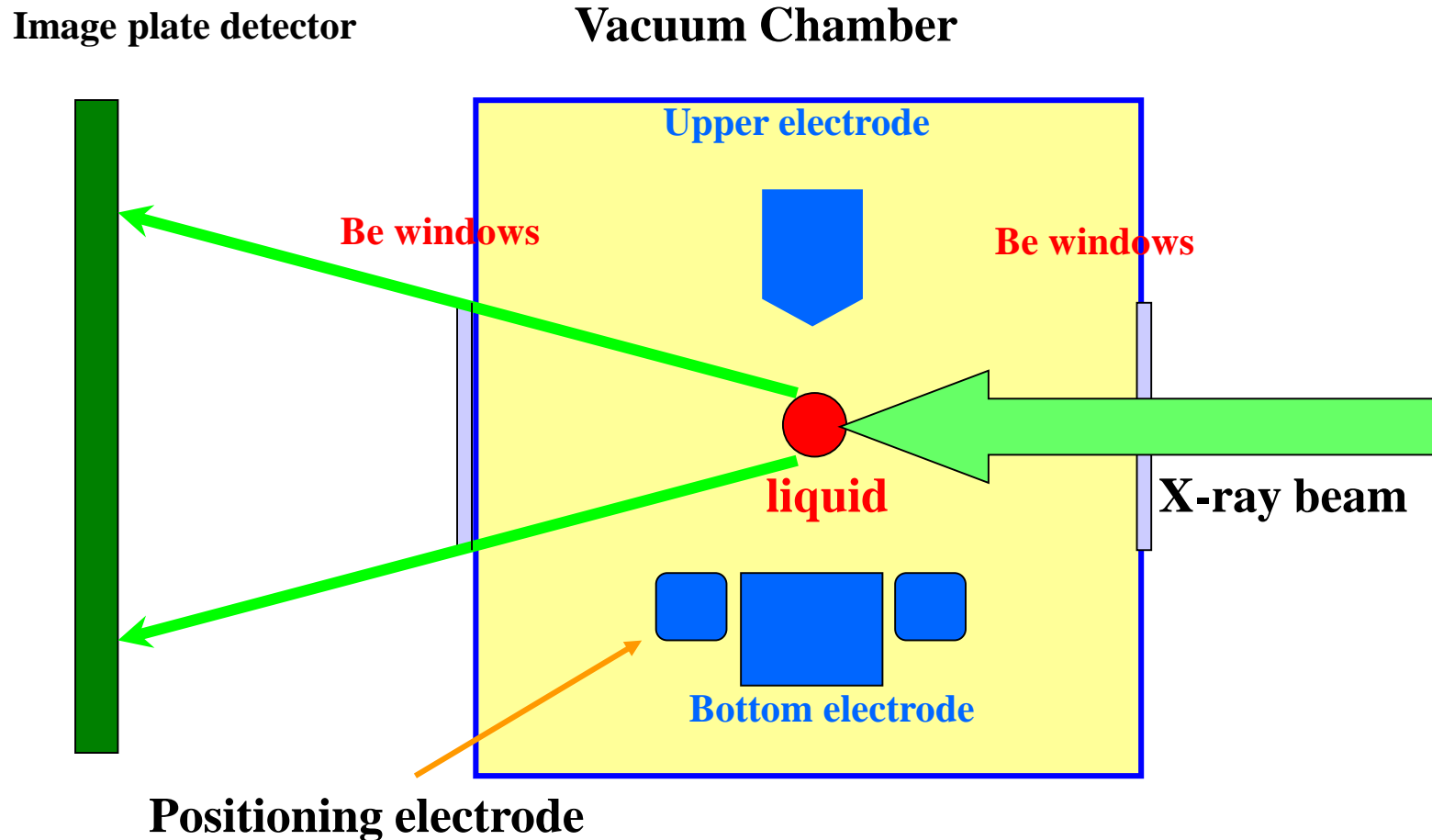
P.-F. Paradisa, et al., JOURNAL OF APPLIED PHYSICS 100, 103523 2006

- Specific heat,
- Emissivity,
- Density,
- Viscosity,
- Surface tension...

Physics Today, v56, p22, July 2003



# Beam-ESL; High-energy synchrotron x-ray scattering experiment



Sample size : 30-100 mg,  
Temperature : 300-2200 K,

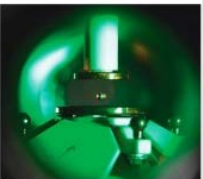
X-ray Energy : 125 keV,  
Vacuum :  $10^{-7}$  torr

Wavelength :  $0.0988 \text{ \AA}$   
Exposure time : 1 sec.

# 인공우주장치로 '건담 합금'도 가능할까

“적 정치를 한 방에 꺾을 강력한 탄환을 만든다. 노르웨이나 휴대전화의 배터리를 사용시간을 수십 배 늘린다.” 지구에서 자연적으로 존재하는 물질로는 이런 소재를 개발하기 어렵다. 지구를 떠나거나 단단한 초금속, 원기재정합을 30배나 늘린 물질이 있어야 하기 때문이다. 과학자들이 대신 찾은 곳은 우주 공간이다. 정확히 말하면 진짜 우주를 본뜬 ‘인공 우주’다.

● 국내 첫 인공우주실험실 국내에서 첫 인공우주실험실이 등장했다. 한국표준과학연구원 연구원은 24년 4억 원을 들여 인공우주 공간 구현을 위한 ‘공중부양장치’를 국내 최초로 개발했다. 우주공간과 비슷한 진공과 무중력의 공간을 만드는 장치다. 세계에서는 흔해져 버렸다. 진공을 만드는 것은 어렵지 않다. 펌프를 켜고 내면 된다. 그럴수록 공력을 잃을까. 이 공력은 지구의 중력에 흡수된 뒤 다시 진공기를 통해 반대 방향으로 밀려온다. 공력 저항이 없다면 진공 안에 물체를 놓으면 우주인처럼 공중에 뜰 게 당연하다. 50kg의 사람이면 0.00002N(뉴턴)의 전기적인 힘을 줘야 된다. 이 장치는 고층의 레이저로 공중에 뜬 물체를 실제 4000G까지 가눌 수 있다. 이단우 연구원은 “정지된 거의 완벽한 상태를 유지해 제자리에서 떠 있을 수 있고 방향을 바꾸거나 지구 상에서와 다르게 움직일 수 있다. 물체에 실을 때와 같은 공간 미세하게 조절한 장치를 완성했다”고 말했다.



공중부양장치는 진공을 이용해 물체를 공중에 띄울 수 있다. 물체의 높이를 공중에서 띄우는 모습. 사진: 한국표준과학연구원

지는 이유는 물질이 결정 형태로 굳어 있기 때문인데 비결정 금속은 결정을 이루지 않아 잘 깨지지 않는다. 이 기술은 원자 장치의 정밀한 제조에 쓰인다. 고밀도 배스, 리튬 등 다양한 첨단물질을 만드는 데 응용되고 있다. 일본 우주항공연구개발기구(JAXA) 연구진은 2006년 비슷한 실험장치를 이용해 전기저장량을 30배나 늘린 배터리의 성능을 높였다. 아마도 인공 우주에도 진짜 우주처럼 할 수는 없다. 그래서 국제우주정거장(ISS)을 거대한 우주항공으로 활용하는 방법은 모색되고 있다. NASA는 이미 우주정거장에 소재 개발을 위한 실험장치를 운영해오고 있으며 일본도 곧 비슷한 장치를 설치할 예정이다. 이단우 연구원은 “제품을 쓰는 국에서 장치를 쓰는 사람이 있어야 할까”라고 묻는 일을 한다. “는 냉소도 없었다”며 “앞으로 이 장치의 활용을 논하더라도 크기의 초미세 반도체 소재를 연구할 계획”이라고 말했다.

대한=전승환 동아사이언스 기자 [ehank@nccok.com](mailto:ehank@nccok.com)



1979년 소개된 만화영화 ‘기동전사 건담’의 주인공 로보트 00-78-2. 이 로보트는 합성소재로 만들어진 인공우주실험실에서 연구될 예정이다. 사진: 한국표준과학연구원

## 세계 8번째 ‘진공-무중력 공간’ 구현 우주와 환경 유사해 각종 실험 가능

인간에게는 금속-저장장치인 배터리의 등 ‘연화성과 같은’ 신소재 개발 기대

장 큰 권위를 ‘미래의 이 장치’를 만든다. 공력이 있는 지구에서 실험할 수 없는 ‘공중부양’이라는 용어가 있다. 다른 물질이 남아 있으니 당연히 실험결과에 오차가 생긴다. 눈높이가 실제 30035에 달하는 오스튬(Cu) 같은 물질은 덩어리 움직이지 않는다. 연구원이 개발한 공중부양장치는 이런 한계를 극복해 ‘공중 실험’을 가능하게 한다. 우주 우주연구기관이 이 장치를 사용할 것으로 전망된다.

● ‘핵미드 인 스페이스’ 신소재 1979년 처음 발명된 일본 에.베이라 ‘기동전사 건담’의 주인공 로보트 00-78-2. 이 로보트는 합성소재로 만들어진 인공우주실험실에서 연구될 예정이다. 사진: 한국표준과학연구원

MOCHO

# '공중부양 측정' 성공

YTN

## 우주환경 구현... 공중부양장치 개발

한국표준과학연구원

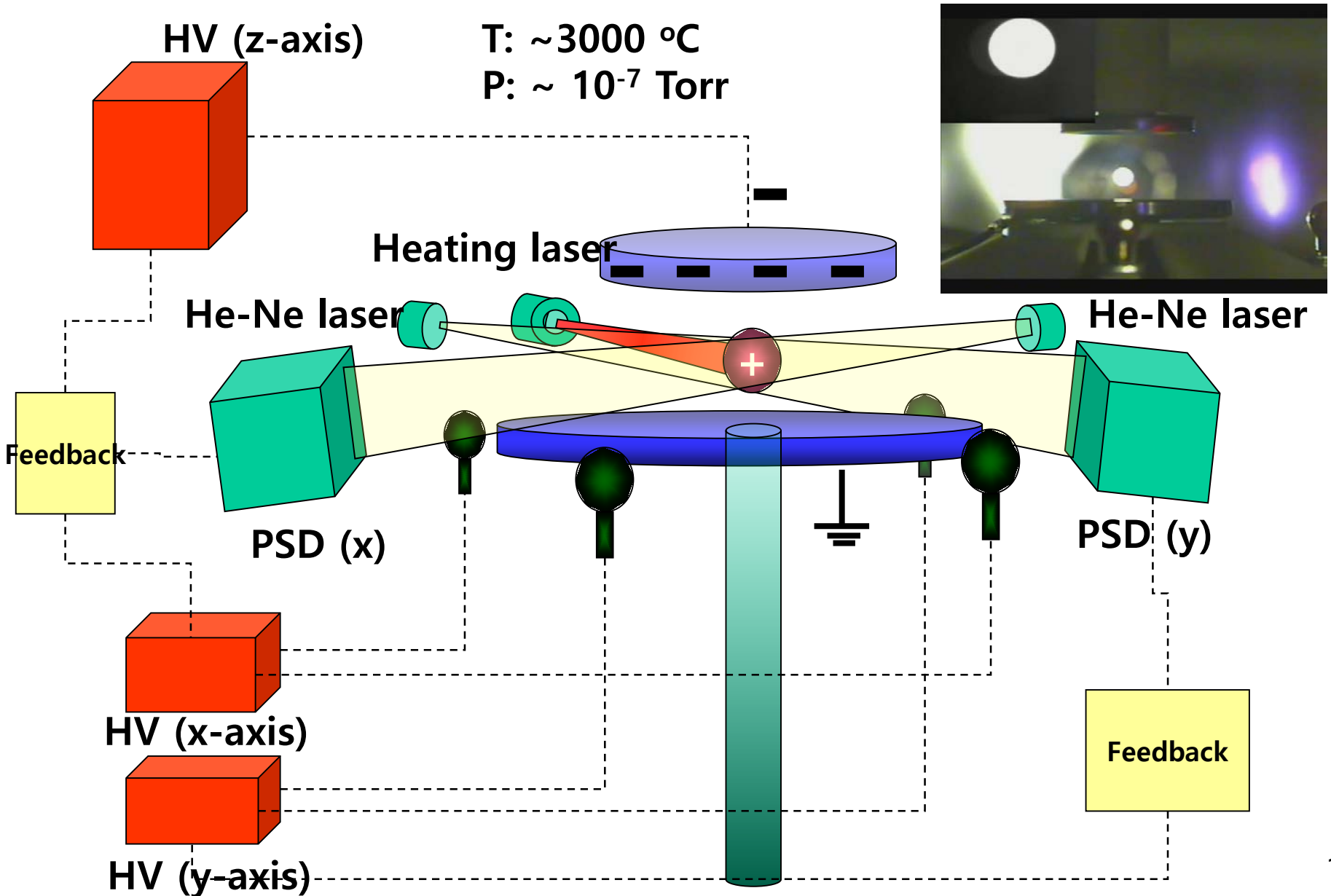
KBS1

## 공중 부양 장치

무선 0.3g

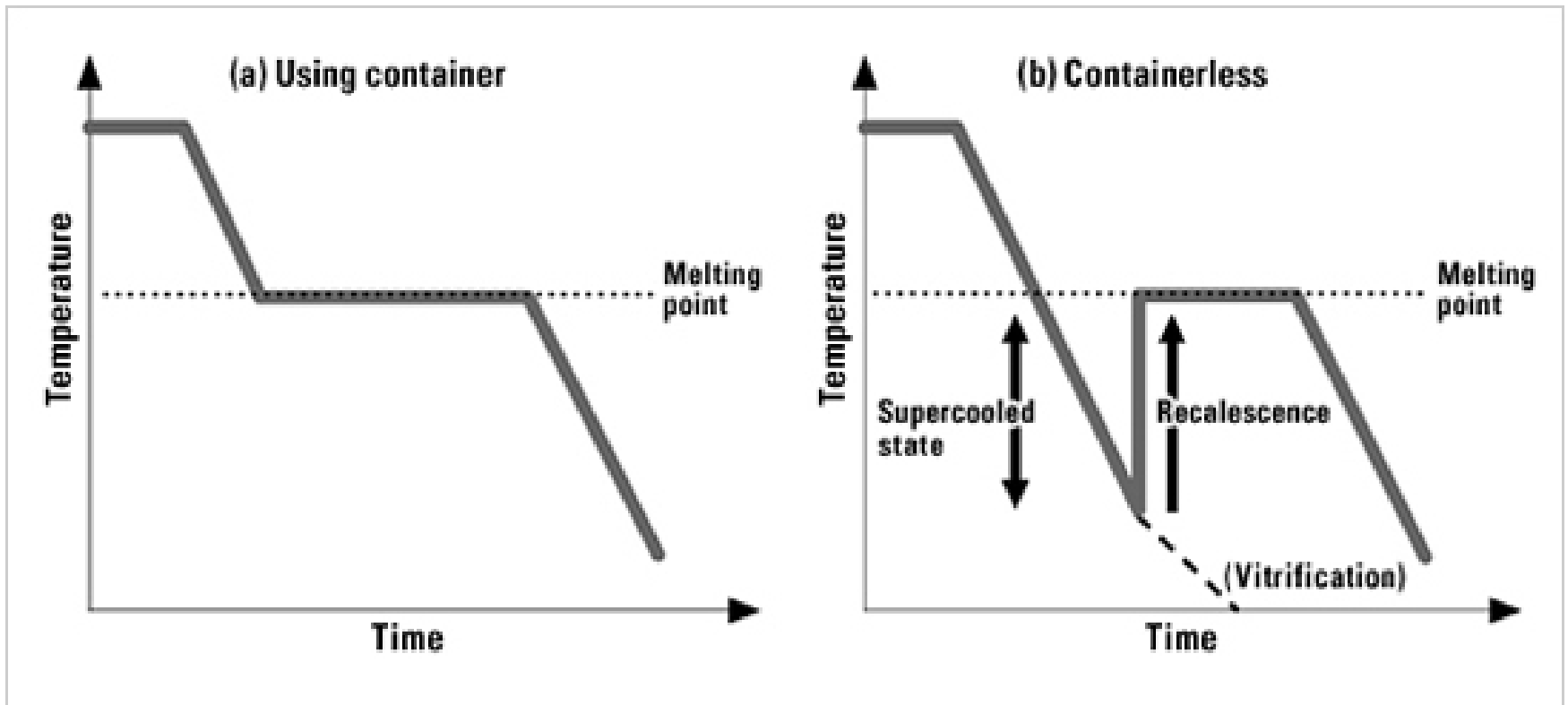
# Electrostatic Levitation in KRISS

Containerless equipment: close to homogeneous nucleation

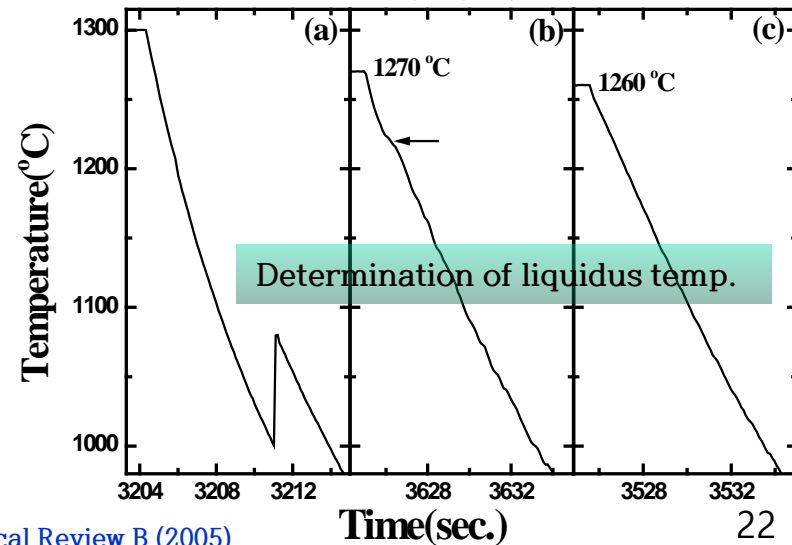
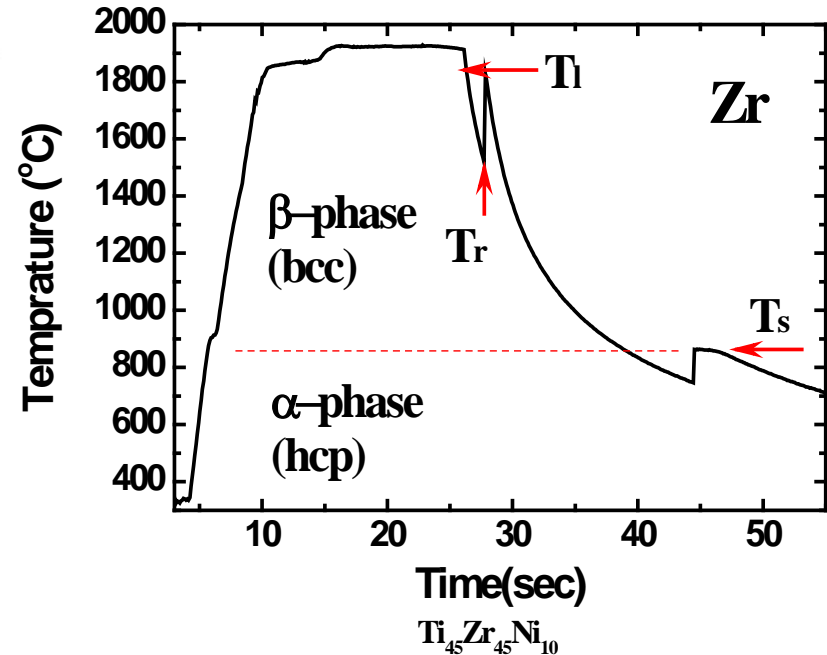
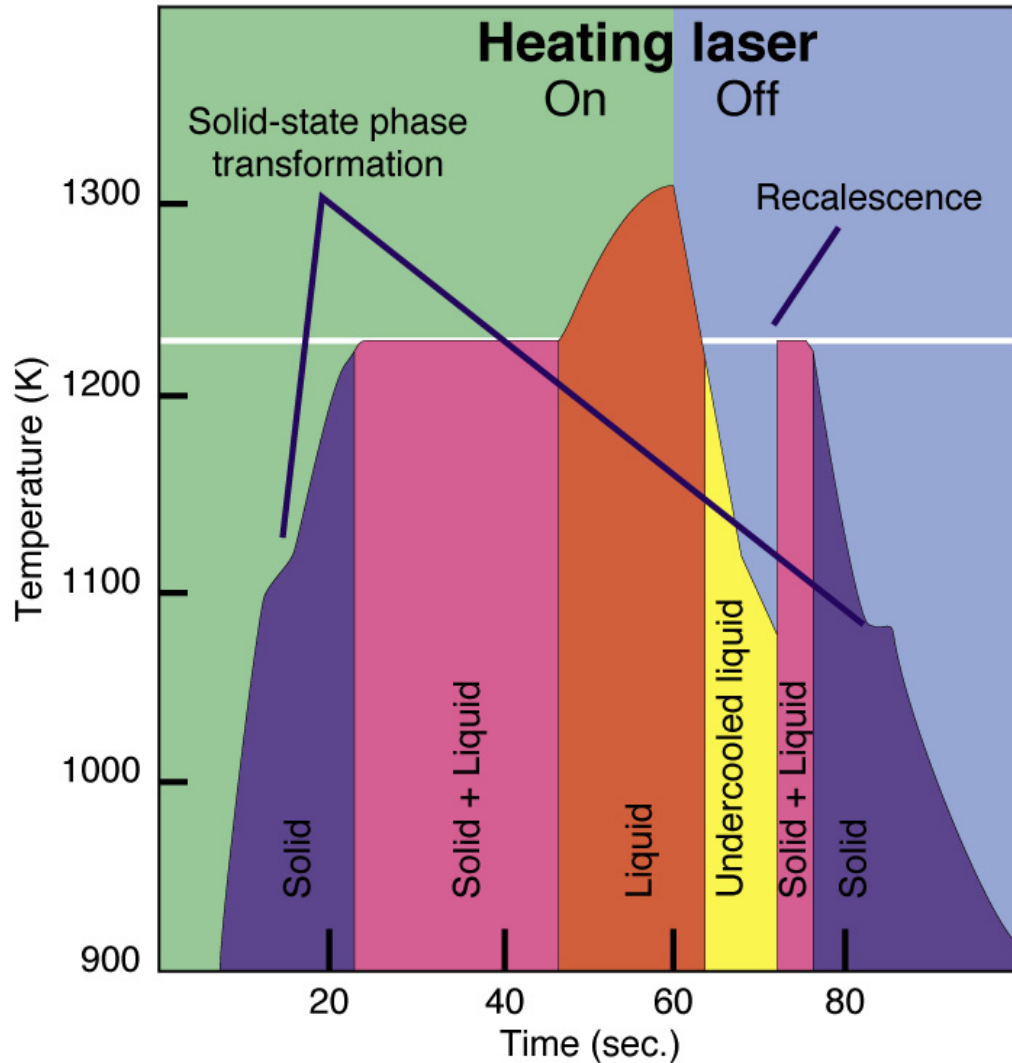




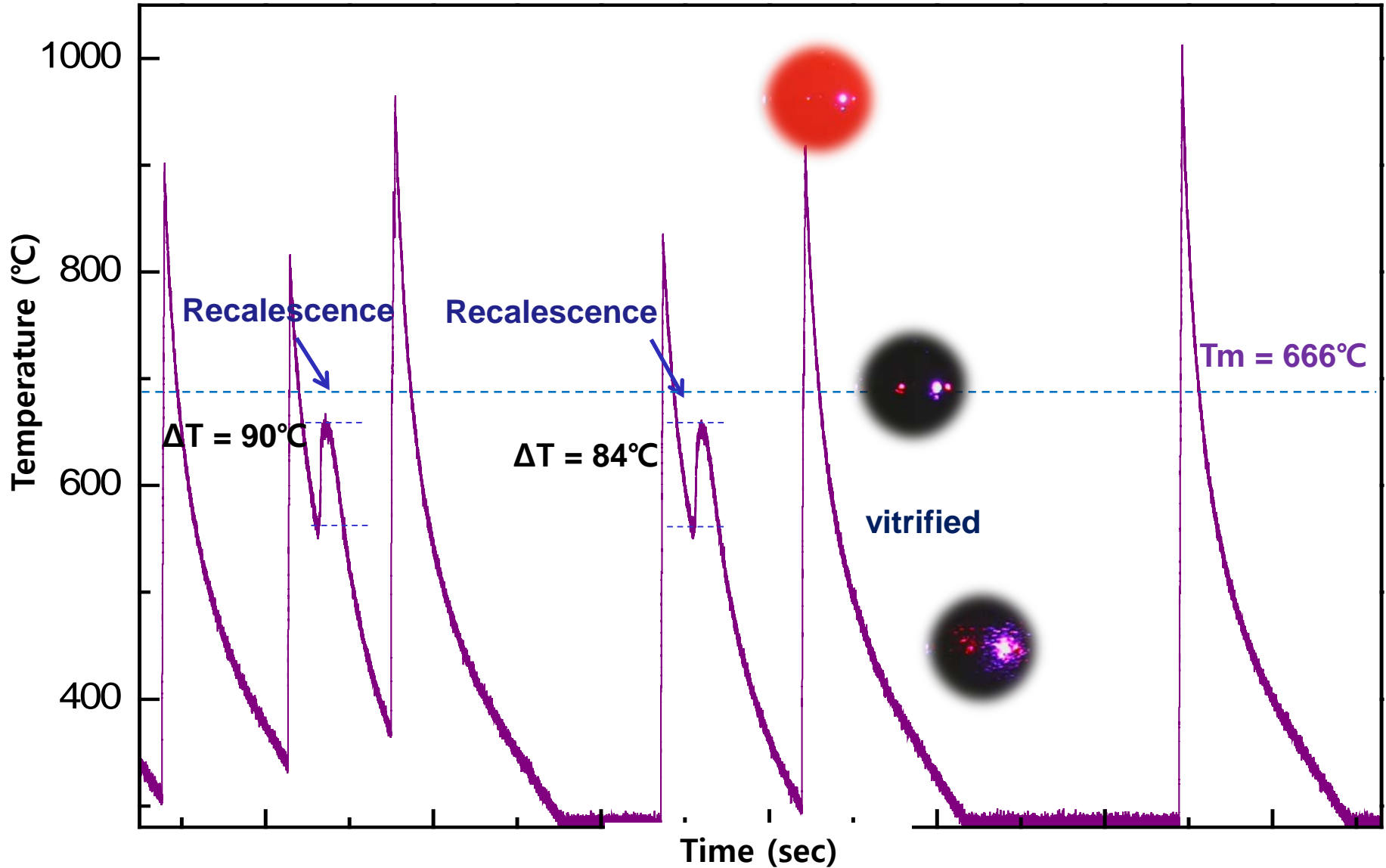
- ▶ No solid containers, No impurities from container
  - No heterogeneous nucleation site
    - Extremely large supercooling can be obtained, clear recalescence
    - Metallic glass can be formed through free cooling



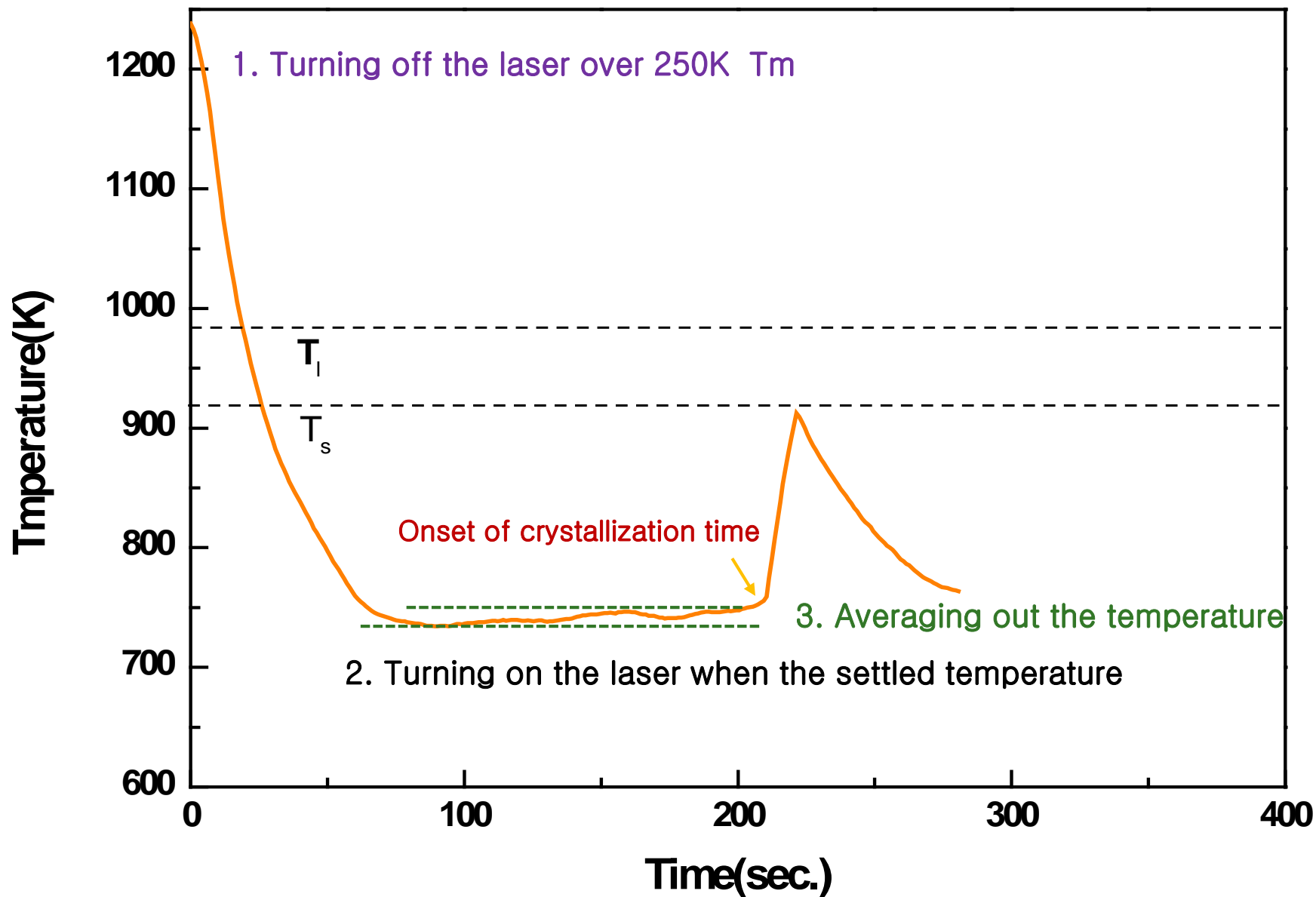
# 1) Melting and Freezing Using ESL



Cyclic cooling curves of  $Zr_{41.2}Ti_{13.8}Cu_{12.5}Ni_{10}Be_{22.5}$

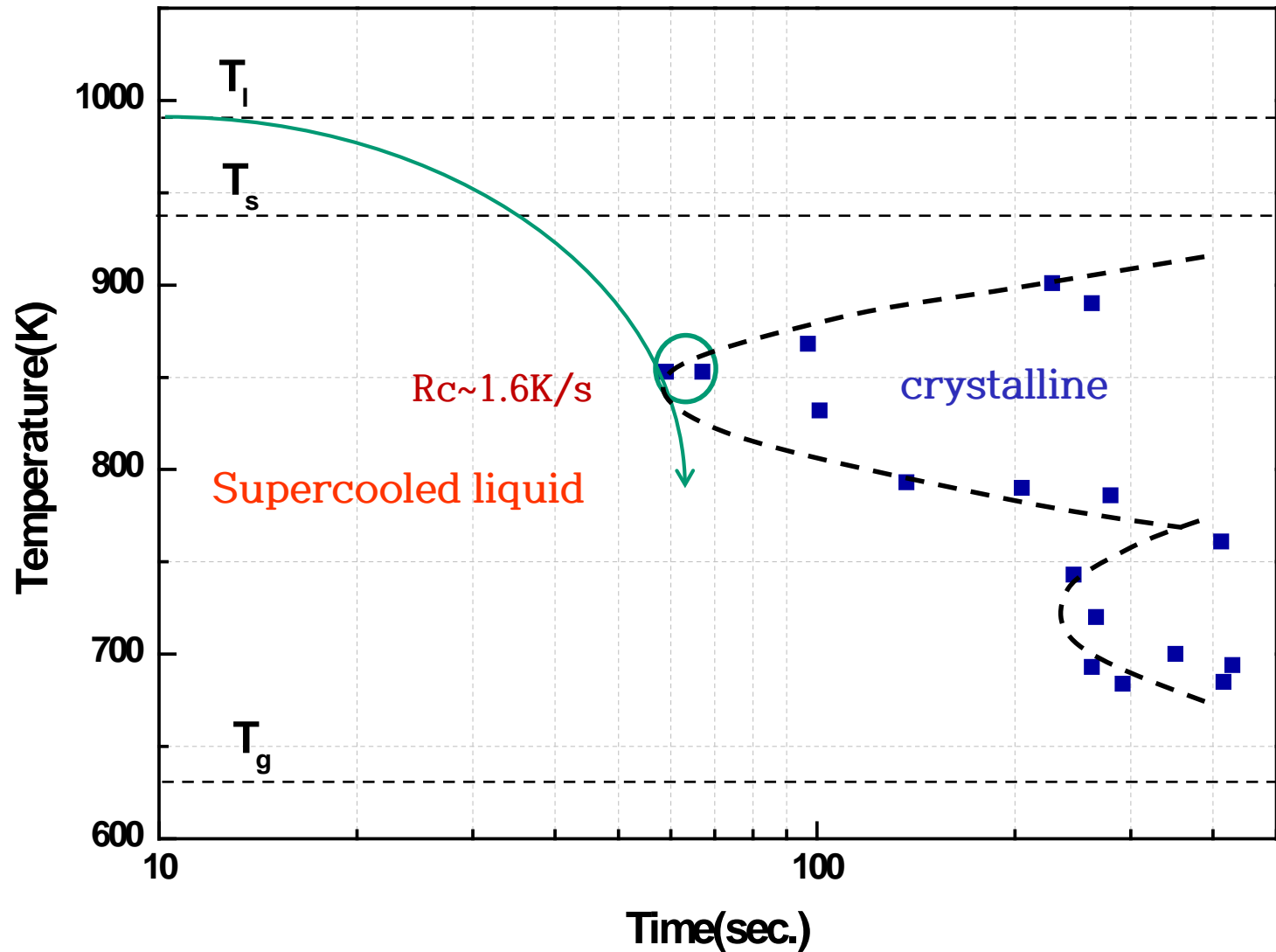


### 3) Measurement of TTT diagram - $Zr_{41.2}Ti_{13.8}Cu_{12.5}Ni_{10}Be_{22.5}$

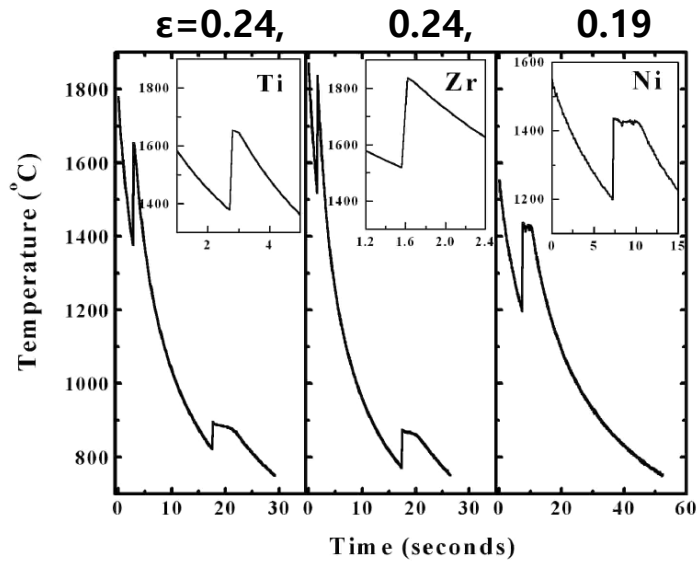




# Measurement of TTT diagram - $\text{Zr}_{41.2}\text{Ti}_{13.8}\text{Cu}_{12.5}\text{Ni}_{10}\text{Be}_{22.5}$



# 4) Specific heat capacity



$$mC_p \left( \frac{dT}{dt} \right) = 4\pi r^2 \sigma \epsilon (T^4 - T_s^4)$$

## Specific heat of pure elements

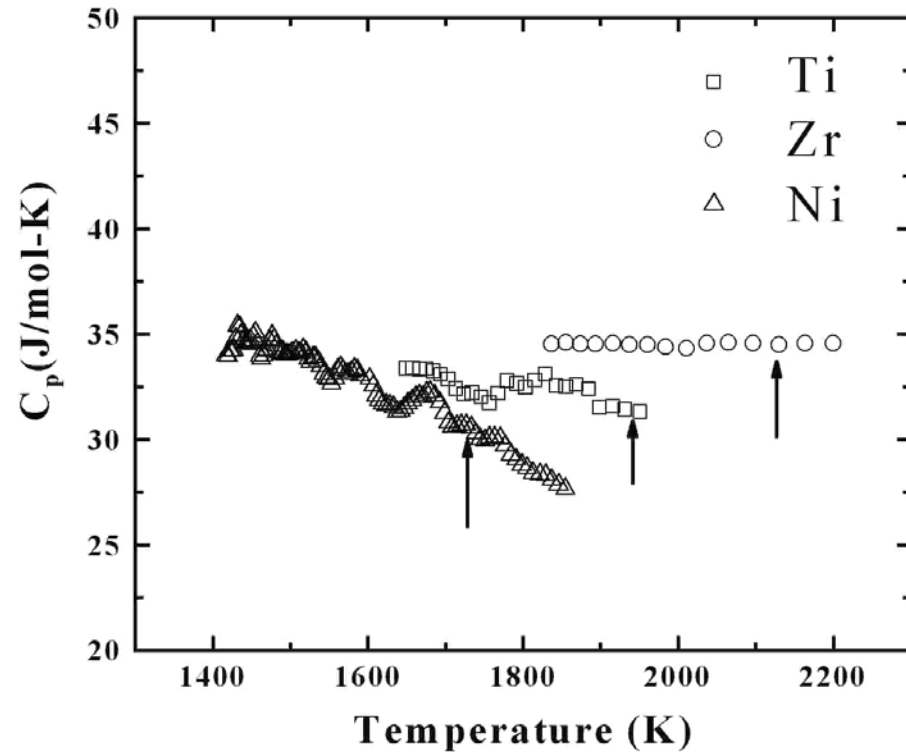
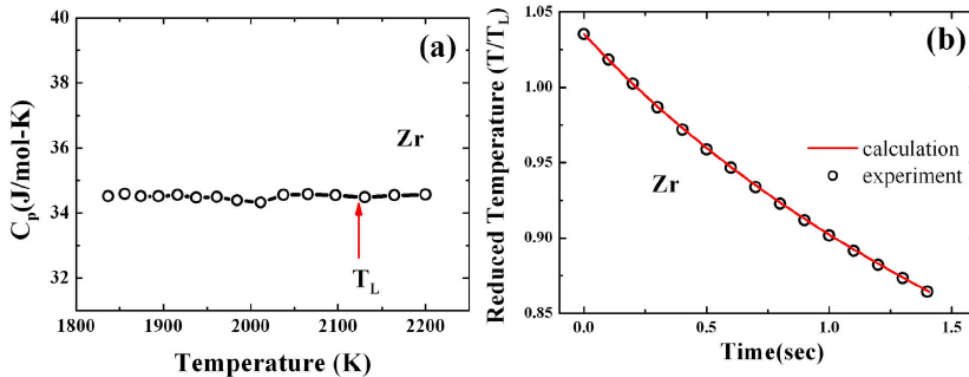


Figure 6.1. Free cooling curves of Ti, Zr and Ni, measured in the ESL. Inset figures show recalescences at high temperature.

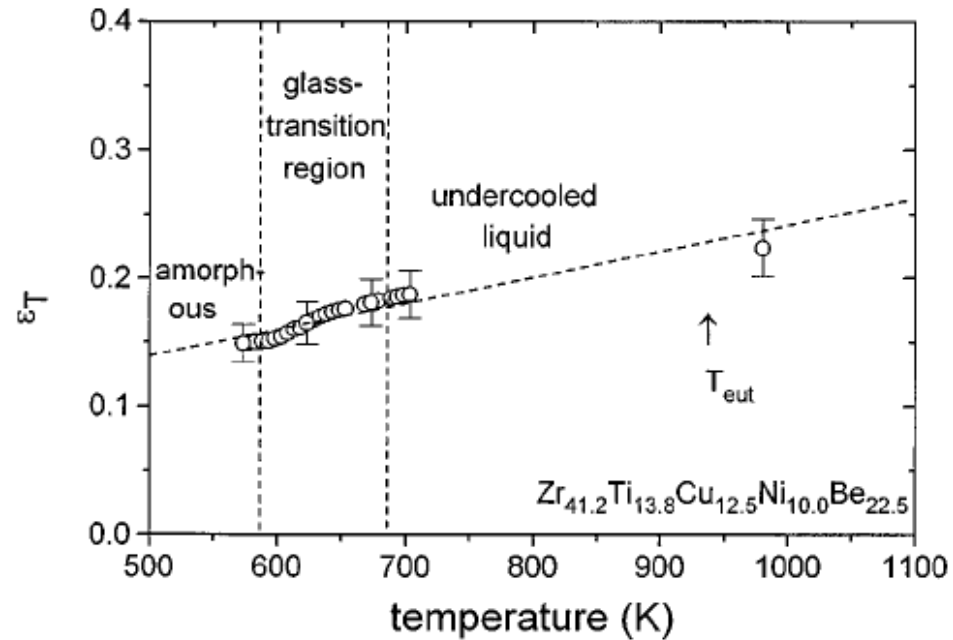
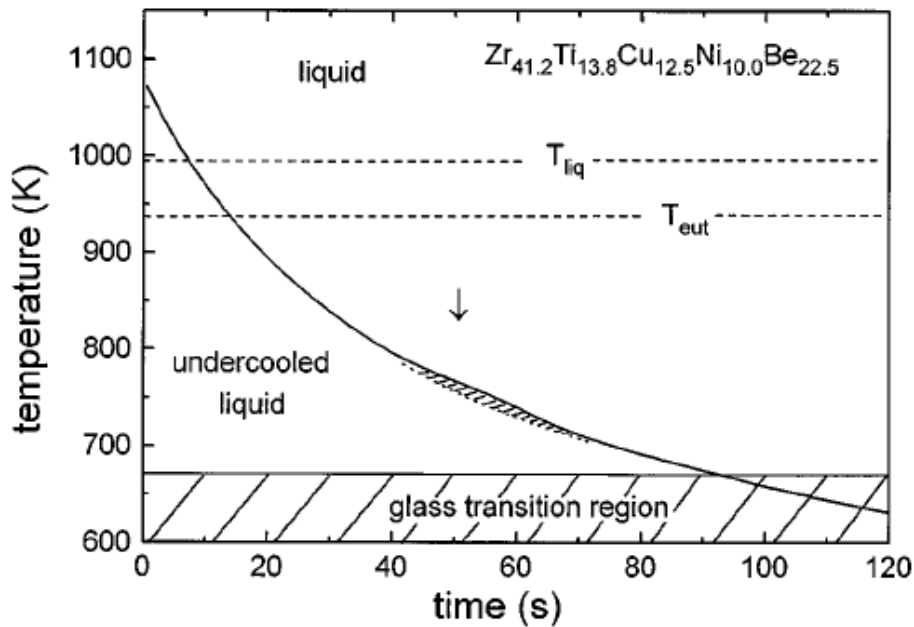


$$t = \frac{mC_p}{4\sigma\epsilon AT_r^3} \left( \ln \left( \frac{(T+T_r)(T_i-T_r)}{(T-T_r)(T_i+T_r)} \right) + 2 \tan^{-1} \left( \frac{T}{T_r} \right) - 2 \tan^{-1} \left( \frac{T_i}{T_r} \right) \right)$$

# 5) Emissivity

$$mC_p \left( \frac{dT}{dt} \right) + Power = 4\pi\sigma\epsilon(T^4 - T_o^4)$$

Steady condition,  $\left( \frac{dT}{dt} \right) = 0$

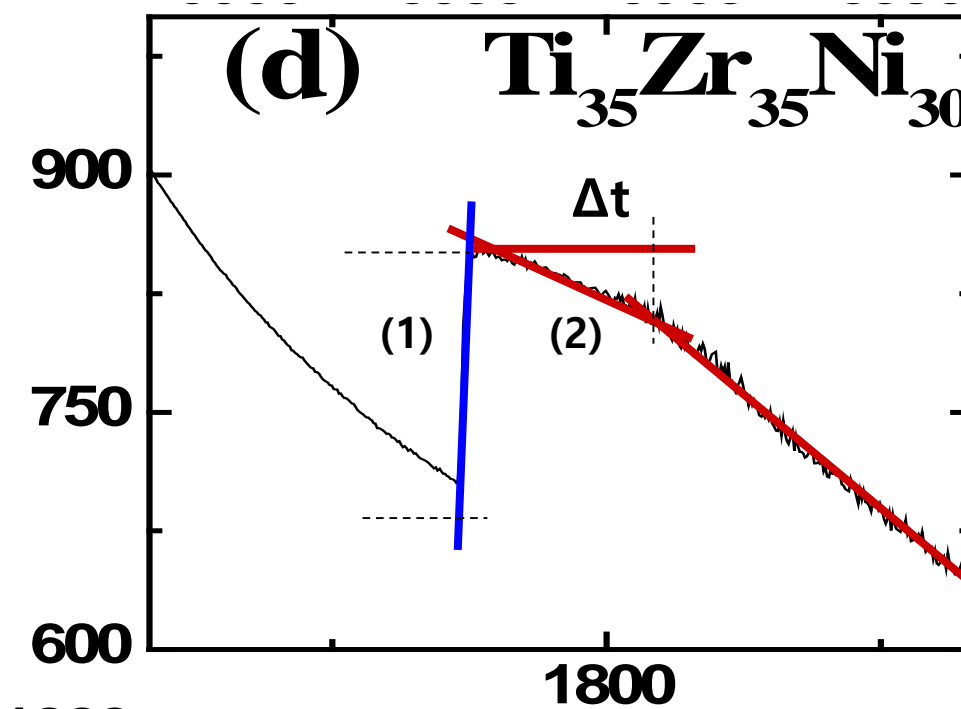


Kim, et.al., APL v68 (1995)

# 6) Fusion Enthalpy

$$\Delta H_f = (1) + (2) = C_p \Delta T_r + (4\pi\sigma\varepsilon(T_P^4 - T_o^4)\Delta t - 4\pi\sigma\varepsilon(T_P^4 - T_{end}^4)\Delta t)$$

Crystallization



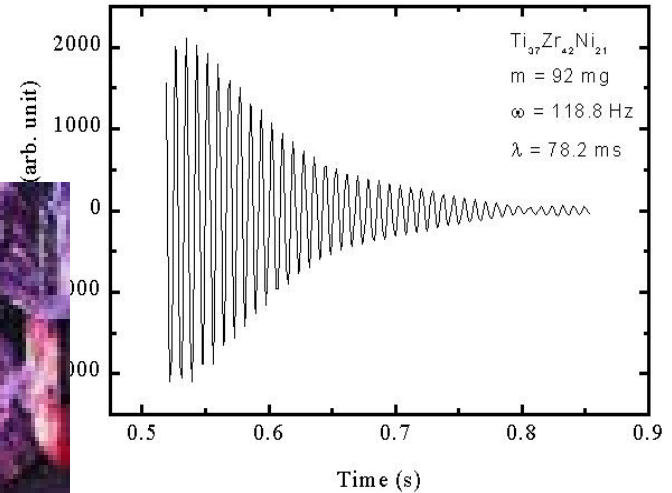
# 7) Viscosity & Surface Tension: Oscillation

## Snapshot of surface oscillations in a Ni droplet



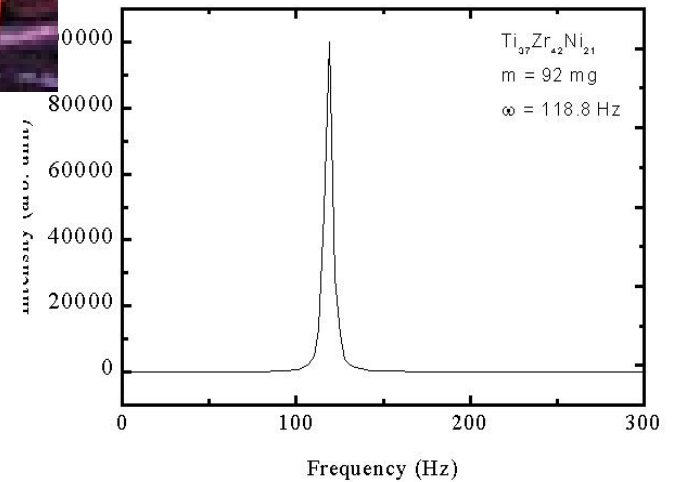
## Damped oscillations

Exponential decay of amplitude



## Power Spectrum

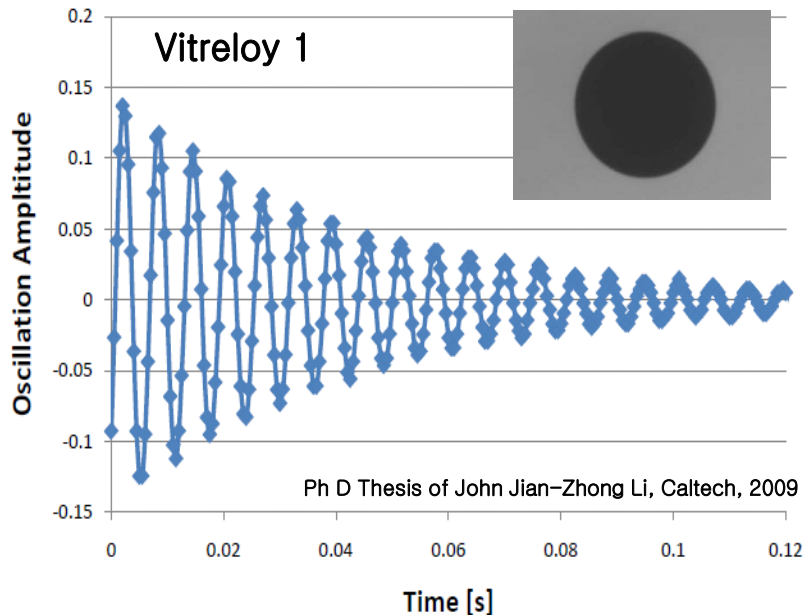
Single frequency



**Caution:** No distortion from spherical symmetry  
allowed multiple modes will be excited

## ► Measurement of thermophysical properties

- Volume : CCD camera / Temperature measurement : pyrometer
- Surface tension & Viscosity : oscillating the sample by with a pulse of AC voltage



$$\omega_2^2 = \frac{8\gamma}{\rho r_0^3}$$

Oscillation frequency

Surface tension

Radius when melt adopts a spherical shape

Density

$$\frac{1}{\tau_2} = \frac{5\eta}{\rho r_0^2}$$

Decay time constant

Viscosity

- Specific heat & total hemispherical emissivity :  $\frac{m}{M} C_P \frac{dT}{dt} = -\sigma_{SB} \epsilon_T A (T^4 - T_S^4)$
- Time- temperature-transformation curve : isothermal treatment

Oscillating drop 방식으로 고온에서 metal의 점도/ 표면 장력 측정 가능

# Oscillating drop

- Induce surface oscillations in a levitating liquid droplet of radius 'R<sub>o</sub>', mass 'm'
- Measure the frequency of oscillation ( $\omega$ )
- Measure the damping constant ( $\lambda$ )

- Damped resonant oscillations:

$$R=R_0(1 + \delta \cos(\omega t)e^{-\lambda t})$$

Rayleigh (1879)

- Resonant frequency determined by surface tension:

$$\omega_l = \sqrt{\frac{l(l-1)(l+2)\gamma}{\rho R_o^3}}$$

- Damping determined by viscosity:

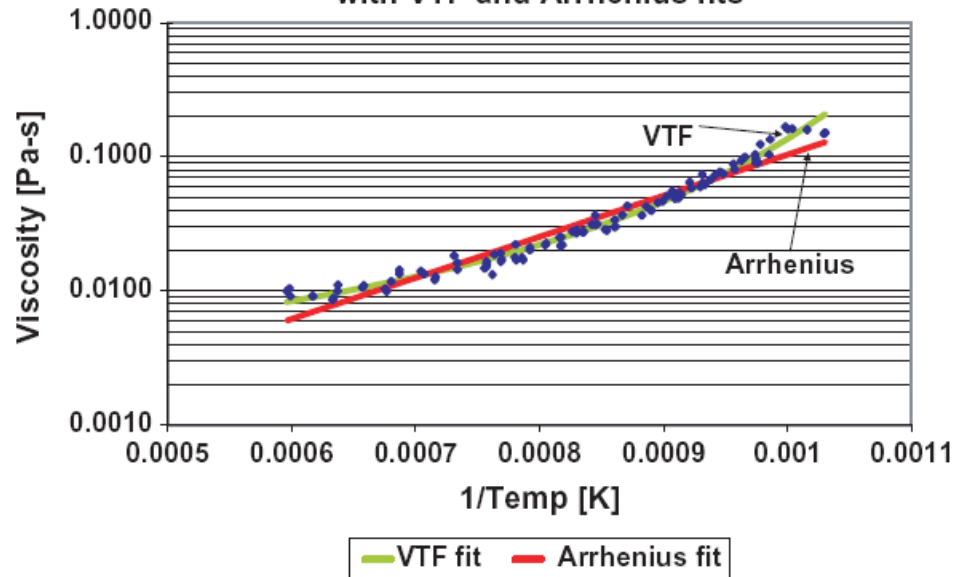
$$\lambda_l = \frac{(l-1)(2l+1)\eta}{\rho R_o^2}$$

Lamb (1881)

# a) High Temp. Viscosity

JOURNAL OF APPLIED PHYSICS 100, 103523 2006

Ti<sub>39.5</sub>Zr<sub>39.5</sub>Ni<sub>21</sub> log Viscosity plot  
with VTF and Arrhenius fits



Hyers, et.al., Philosophical Magazine Vol. 86, 2006(341-347)

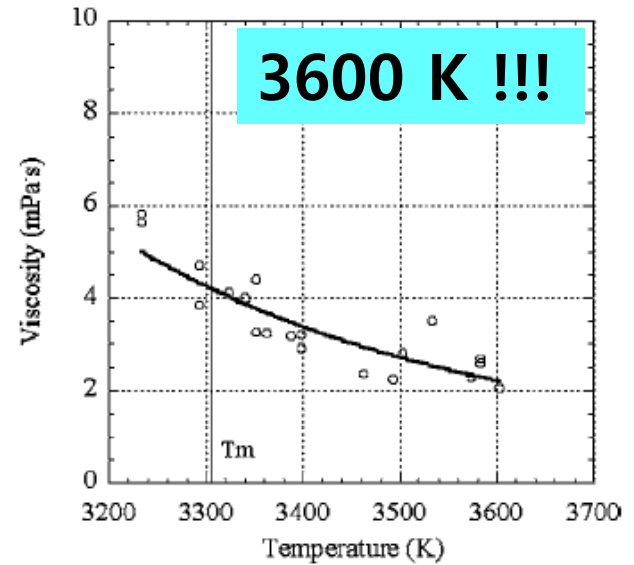


FIG. 5. Viscosity of equilibrium and nonequilibrium liquid Os as a function of temperature

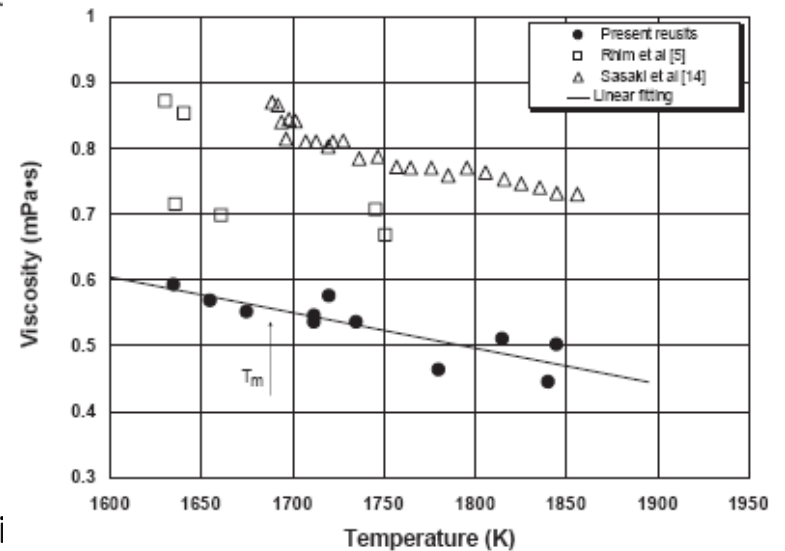


Fig. 8. Viscosity of molten silicon as a function of temperature.



# b) High Temp. Surface Tension

Hyers, et.al., Philosophical Magazine Vol. 86, 2006(341–347)

JOURNAL OF APPLIED PHYSICS 100, 103523 2006

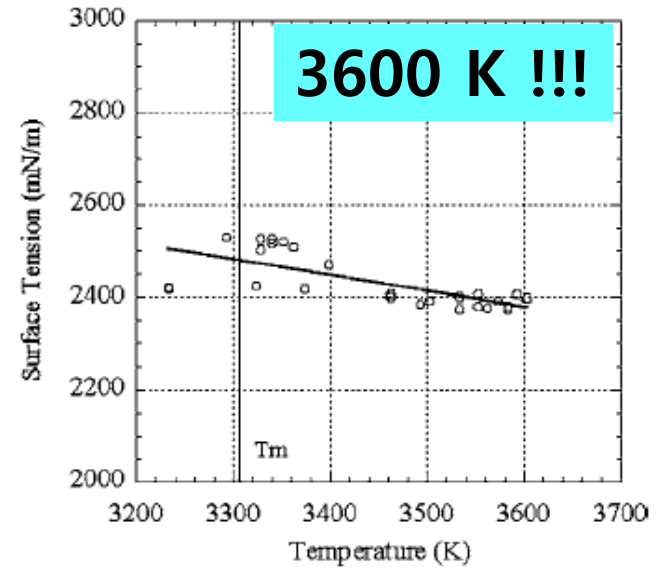
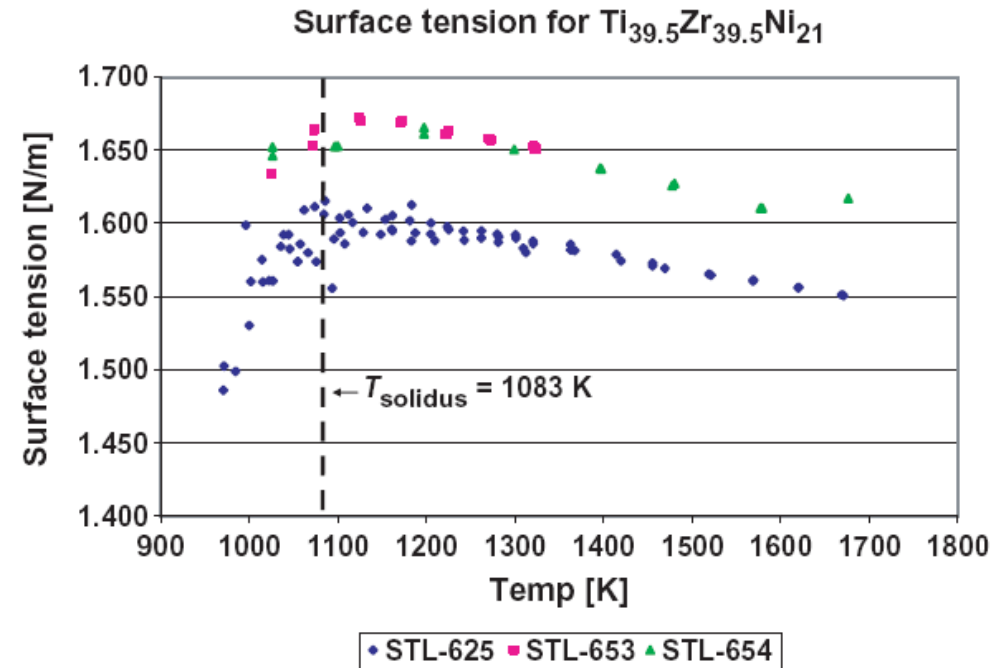


FIG. 4. Surface tension of equilibrium and nonequilibrium liquid Os as a function of temperature.

# c) Density

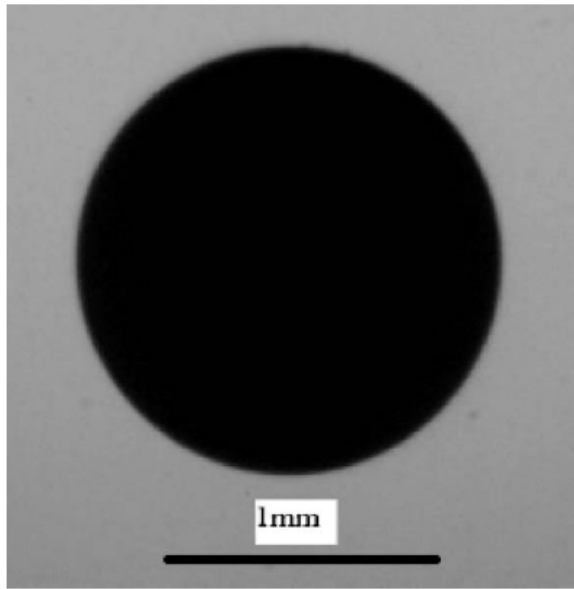


Fig. 2. A typical side view of a levitated molten silicon from which the density and the specific volume could be extracted.

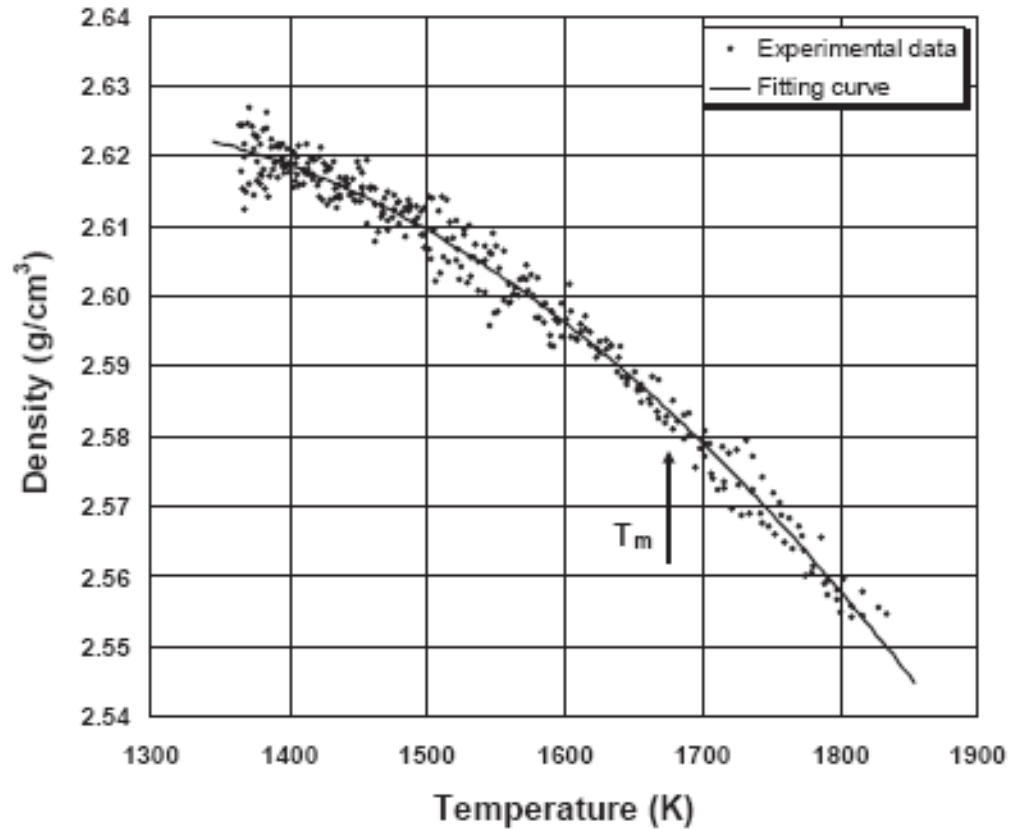


Fig. 4. Temperature dependent density of molten silicon.

Paradis, et.al., JOURNAL OF APPLIED PHYSICS 100, 103523 2006

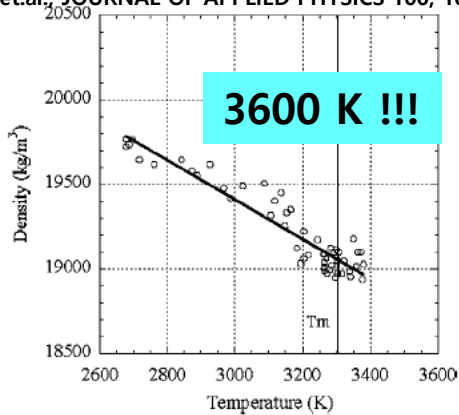
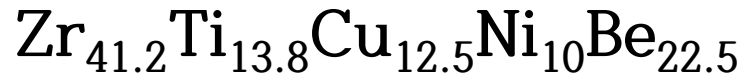
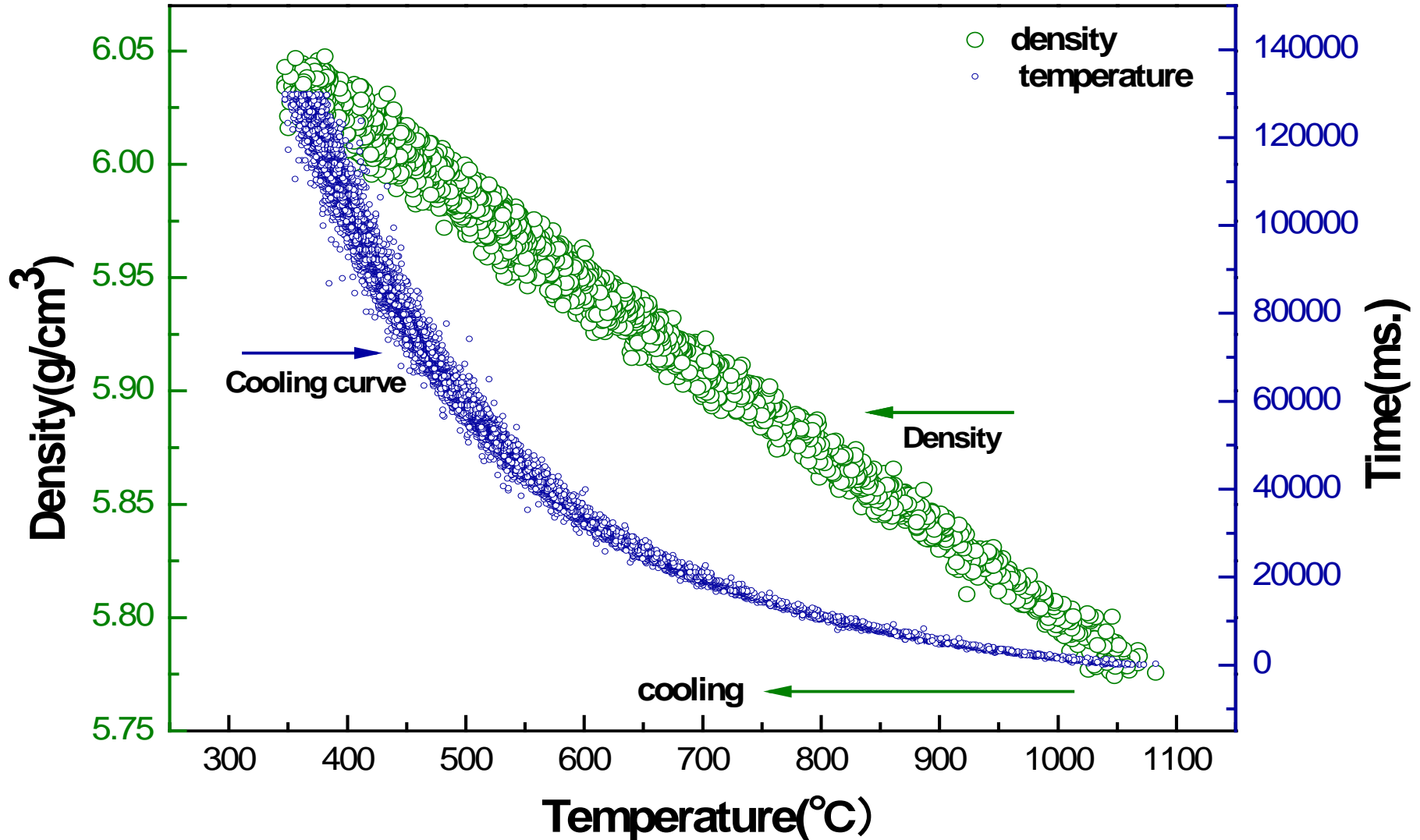


FIG. 3. Density of equilibrium and nonequilibrium liquid Os as a function of temperature.

# Cooling curve and density temperature profiles of



- Volume : CCD camera / Temperature measurement : pyrometer



# Crystallization: Undercooling of Os

Paradis, et.al., JOURNAL OF APPLIED PHYSICS 100, 103523 2006

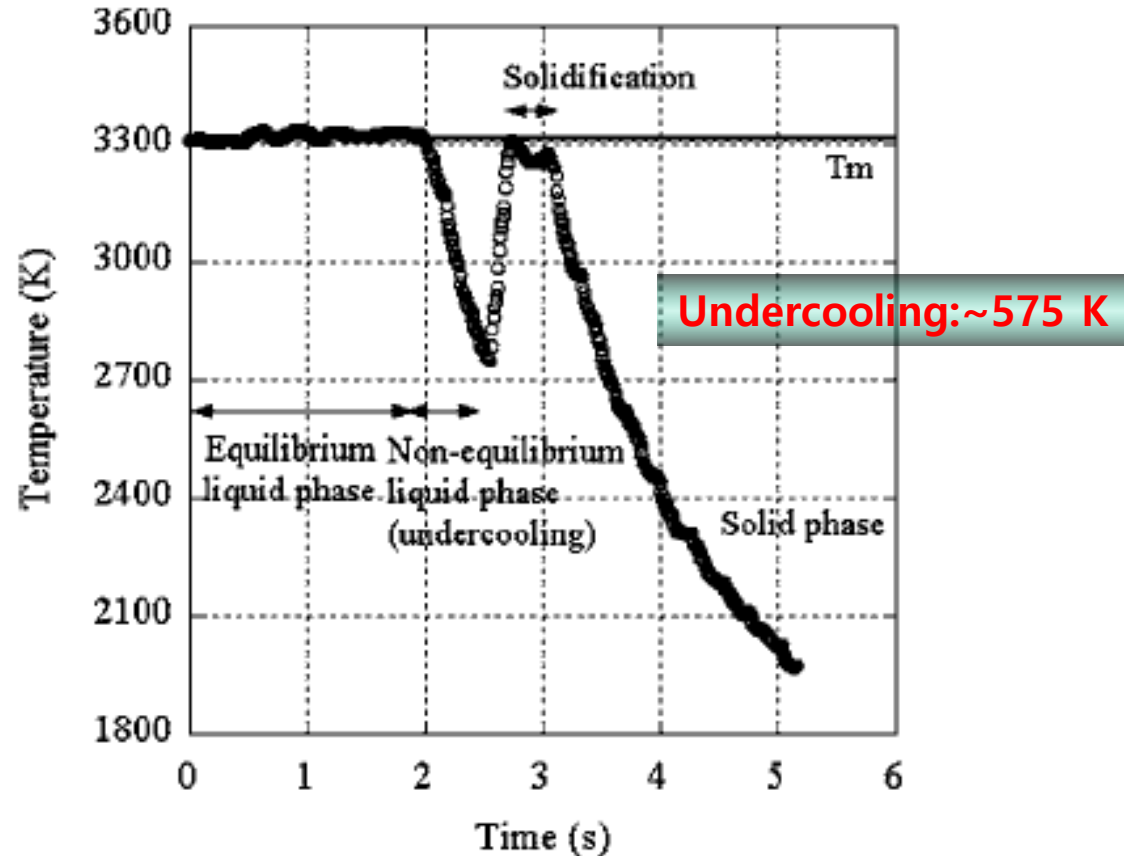
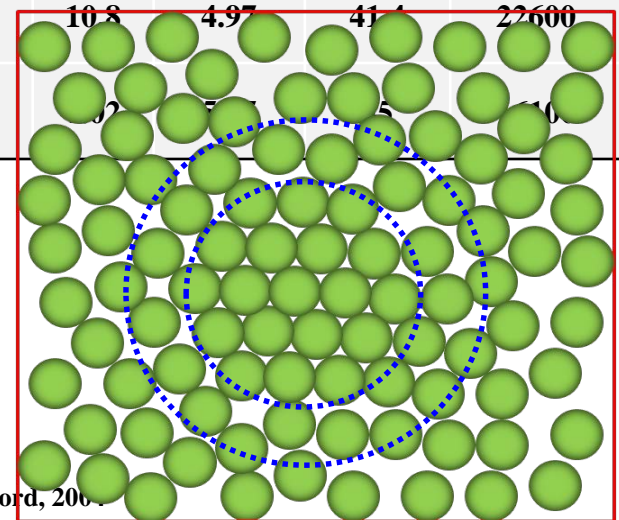


FIG. 2. Temperature history for an Os sample (diameter:  $\sim 1.76$  mm; mass: 64.18 mg) showing heating slightly above the melting temperature ( $\sim 3340$  K), a radiative cooling rate of 1015 K/s, an undercooling of  $\sim 575$  K, recalescence, and solidification.

# Interfacial free energy of some elements

	$\frac{\Delta T_r}{\Delta T_{hyp}}$	$\sigma$ <sup>[1]</sup>	$\sigma$	$\alpha = \frac{\sigma}{\Delta H_f}$	$r^*$	$\rho$	$\eta_m$ <sup>[2]</sup>	$C_p$	$\Delta H_f$ <sup>[3]</sup>
	(K)	(J/m <sup>2</sup> )	(J/m <sup>2</sup> )		(nm)	(g/cm <sup>3</sup> )	(10 <sup>-3</sup> Pa/s)	(J/mol·K)	(J/mol)
Ti	309 341	0.168	0.141 0.152	0.42 0.454	1.46 1.43	4.11	5.2	42.67	14550
Zr	332 345	0.158	0.154±0.009 0.159±0.010	0.410 0.423	1.54 1.52	6.08	4.67	42.5	19300
Hf	339 339	0.229	0.193±0.012	0.404	1.47	12.24	7.07	60.3	24070
Nb	443 563	0.262	0.258±0.016 0.303±0.024	0.394 0.462	1.33 1.23	7.63	4.94	52.0	29300
Rh	413 546	0.279	0.261±0.018 0.313±0.029	0.439 0.527	1.08 1.19				
Fe	195 357	0.269	0.158 0.228	0.33 0.478	1.45 1.15				

- **Turnbull :  $\alpha = 0.45$  for most metals**



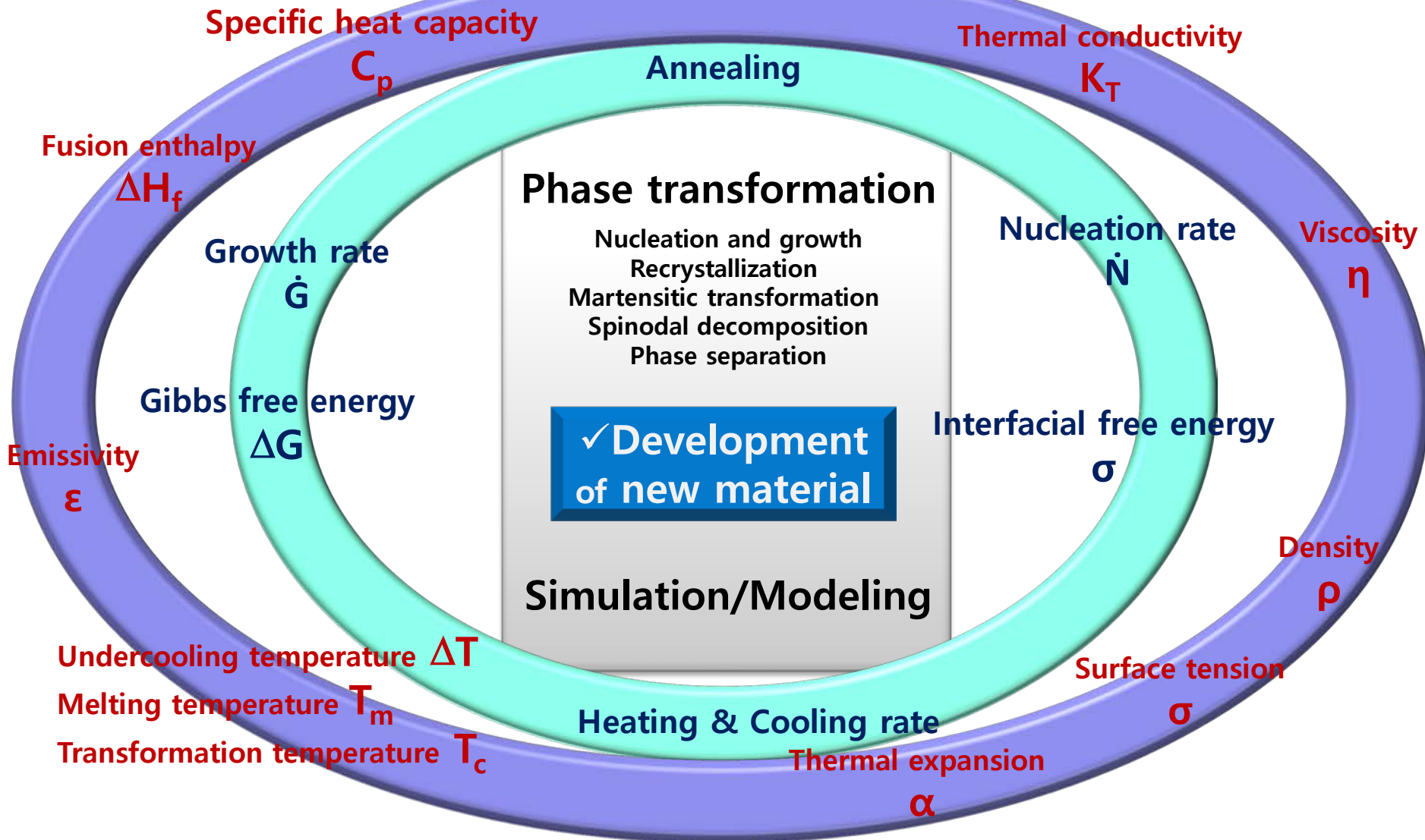
<sup>1)</sup> B. Vinet, L. Magnusson, H. Fredriksson, P. J. Desré, *J. Colloid Interf. Sci.* 255 (2002) 363

<sup>2)</sup> T. Ishikawa, P.-F. Paradis, J. T. Okada, Y. Watanabe, *Meas. Sci. Technol.* 23 (2012) 025305

<sup>3)</sup> W. F. Gale, T. C. Totemeier, in "Smithells Metals Reference Book", 8<sup>th</sup> ed. Butterworth-Heinemann, Oxford, 2000.

# Development of extreme condition endurance materials

## Thermophysical properties



## 3.2. Equilibrium condition for a curved interface

### Stability of curved interface

#### 1) Atomic consideration

##### a) Equilibrium: Geometrical factors $G_F = G_M$ (planer interface)

→ If it is curved, “escape angle” changes with curvature.

①  $S \rightarrow L$ : if Solid is convex structure  $\rightarrow G_M \uparrow$ , concave structure  $\rightarrow G_M \downarrow$   
 $\Delta G_M \propto \text{curvature of the surface} \propto 1/r$

→ if “Spherical” crystal containing  $n$  atoms  $\propto n^{1/3}$

②  $L \rightarrow S$ : reverse direction of ( $S \rightarrow L$ ) case

$\therefore G_M^n$  for  $S \rightarrow L$  transition

for atoms at the surface of a spherical crystal containing  $n$  atoms

$$G_M^n = (1 + \alpha/n^{1/3}) G_M, \quad G_F^n = (1 - \alpha/n^{1/3}) G_F$$

Convex surface = less firmly bound = fewer nearest neighbors in the crystal

→ easier escape than that of flat surface

## b) Average energy for escape

$$L^n = (1 - \beta/n^{1/3}) L_1$$

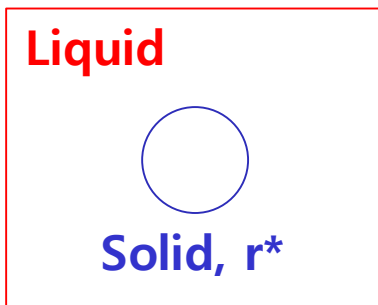
→  $\beta$  is calculated from the number of neighbors  
(ex. FCC structure:  $\beta = 1.33$ )

If the rate for the melting process  $\uparrow \rightarrow r \downarrow$  &  
the rate for the freezing process  $\downarrow \rightarrow T_E \downarrow$ .

$$\therefore T_{E, \text{small crystal}} < T_{E, \text{large crystal}}$$

Thus, at any temperature below  $T_E$ , there is a radius of curvature at which the rates of melting and of freezing are equal.

= critical radius  $r^*$



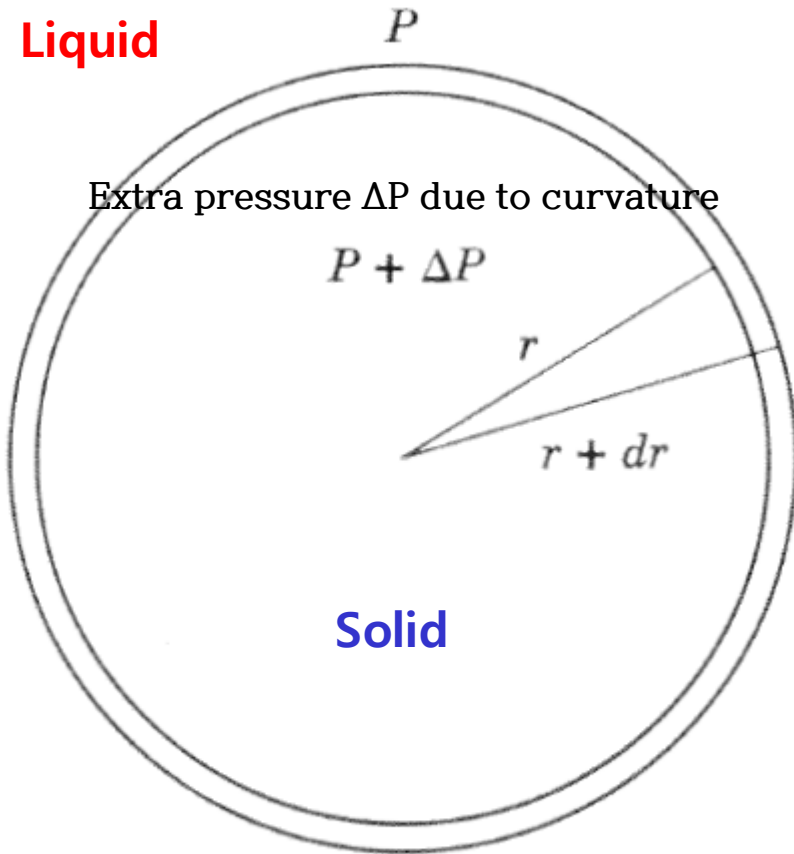
a) if  $T_E + \Delta T (+)$ ,  $R_M > R_F \rightarrow r \downarrow$   
 $\rightarrow T_E \rightarrow T_E' \downarrow \rightarrow \Delta T (+) \uparrow \rightarrow R_M \gg R_F$

b) if  $T_E + \Delta T (-)$ ,  $R_M < R_F \rightarrow r \uparrow$   
 $\rightarrow T_E \rightarrow T_E'' \uparrow \rightarrow \Delta T (-) \uparrow \rightarrow R_M \ll R_F$



## 2) Thermodynamic treatment of equilibrium across a curved interface

Liquid



$$r \rightarrow r + dr, P \rightarrow P + \Delta P$$

The work done is equal to the increase in free energy of the interface; Thus,

$$P dr \times 4\pi r^2 = [4\pi (r + dr)^2 - 4\pi r^2] \sigma$$

whence

$$P = \frac{2\sigma}{r}$$

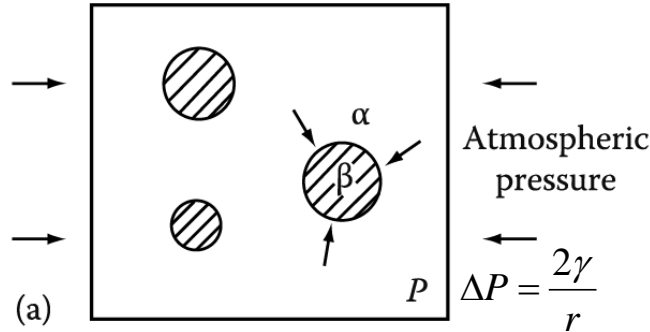
Fig. 3.1. Pressure due to surface tension.

The G curves so far have been based on the molar Gs of infinitely large amounts of material of a perfect single crystal. Surfaces, GBs and interphase interfaces have been ignored.

## 1.6 Influence of Interfaces on Equilibrium

$$\Delta G = \Delta P \cdot V \Rightarrow \Delta G = \frac{2\gamma V_m}{r}$$

Extra pressure  $\Delta P$  due to curvature of the  $\alpha/\beta$



The concept of a pressure difference is very useful for spherical liquid particles, but it is less convenient in solids (often nonspherical shape).

$$dG = \Delta G_\gamma dn = \gamma dA \quad \Delta G_\gamma = \gamma dA/dn$$

Since  $n=4\pi r^3/3V_m$  and  $A = 4\pi r^2$   $\Delta G = \frac{2\gamma V_m}{r}$

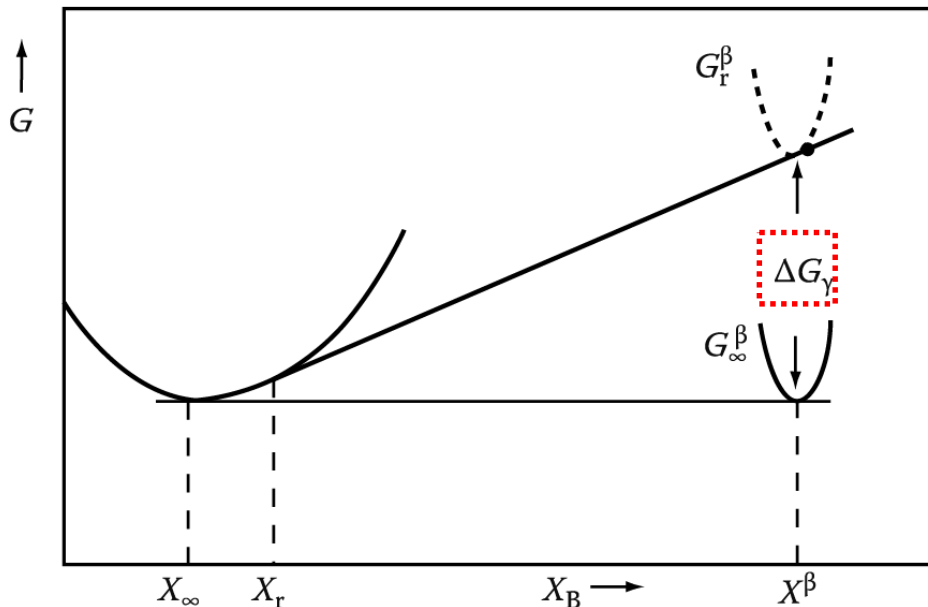


Fig. 1.38 The effect of interfacial E on the solubility of small particle

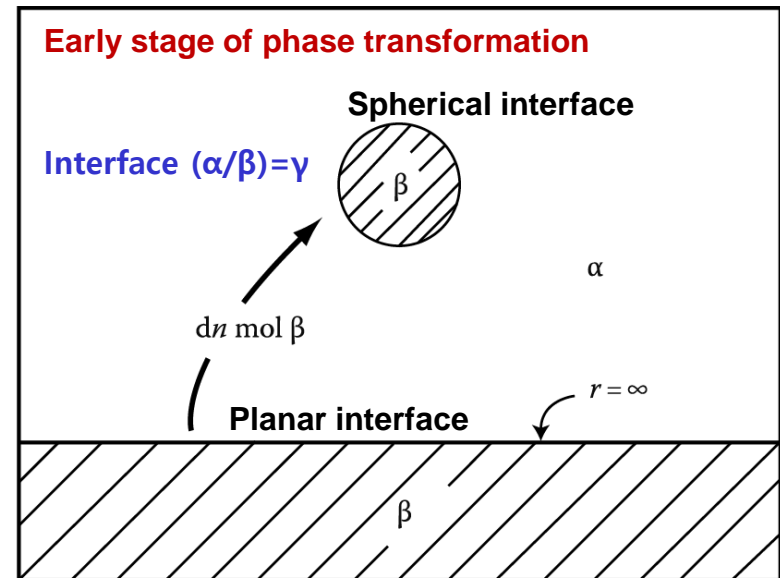


Fig. 1.39 Transfer of  $dn$  mol of  $\beta$  from large to a small particle.

**Gibbs-Thomson effect (capillarity effect):**  
 Free energy increase due to interfacial energy

Quite large solubility differences can arise for particles in the range  $r=1-100$  nm. However, for particles visible in the light microscope ( $r>1\mu\text{m}$ ) capillarity effects are very small.

$$X_B^e = A \exp\left\{-\frac{Q}{RT}\right\}$$

$$X_B^e = \exp\left(-\frac{\Delta G_B + \Omega}{RT}\right)$$

$$X_B^{r=\infty} = \exp\left(-\frac{\Delta G_B + \Omega}{RT}\right)$$

$$X_B^{r=r} = \exp\left(-\frac{\Delta G_B + \Omega - 2\gamma W_m / r}{RT}\right)$$

$$= X_B^{r=\infty} \exp\left(\frac{2\gamma W_m}{RT r}\right)$$

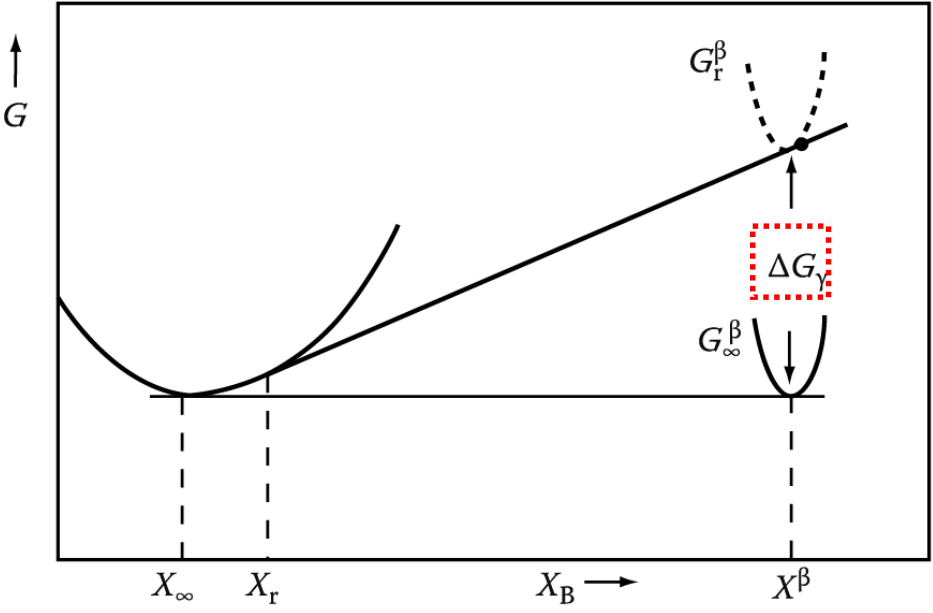
For small values of the exponent,

$$\frac{X_B^{r=r}}{X_B^{r=\infty}} = \exp\left(\frac{2\gamma W_m}{RT r}\right) \approx 1 + \frac{2\gamma W_m}{RT r}$$

Ex)  $\gamma=200\text{mJ/m}^2$ ,  $V_m=10^{-5}\text{ m}^3$ ,  $T=500\text{K}$

$$\frac{X_r}{X_\infty} = 1 + \frac{1}{r(\text{nm})}$$

For  $r=10$  nm, solubility  $\sim 10\%$  increase



(b) Fig. 1.38 The effect of interfacial energy on the solubility of small particles.

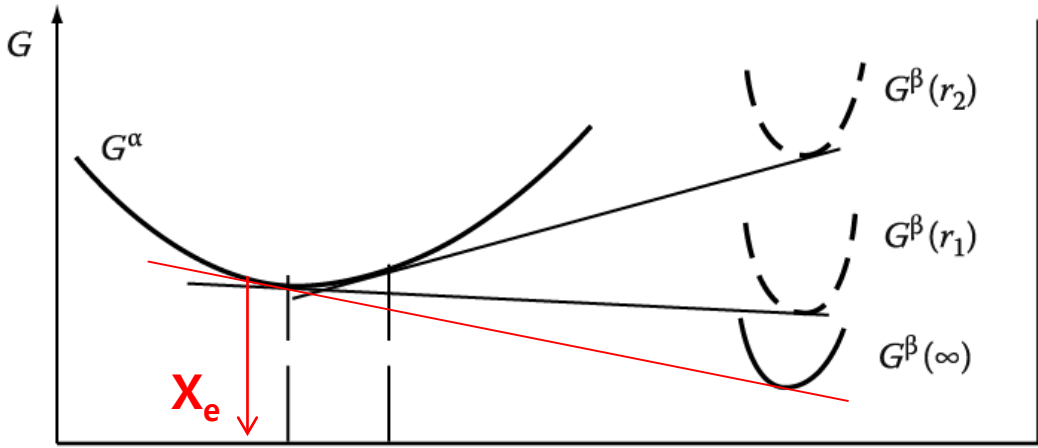
Microstructure of a two phase alloy is always unstable if the total interfacial free E is not a minimum. →

# 5.5.6. Particle Coarsening

(smaller total interfacial area → loss of strength or disappearance of GB pinning effect → particular concern in the design of materials for high temp. applications)

## Two Adjacent Spherical Precipitates with Different Diameters

(Gibbs-Thomson effect: radius of curvature ↓ →  $X_B$  ↑) Assumption: volume diffusion is the rate controlling factor



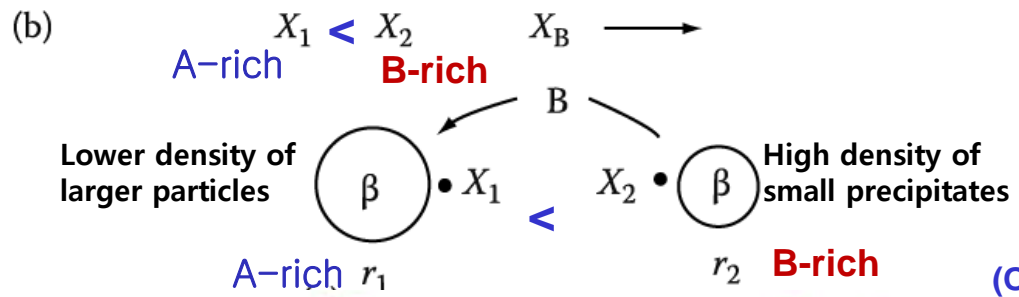
$$(\bar{r})^3 - r_0^3 = kt$$

Average radius

where  $k \propto D\gamma X_e$

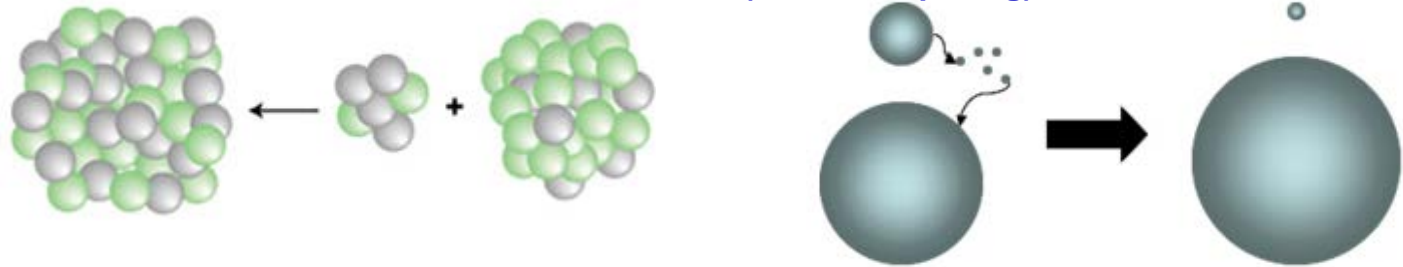
( $X_e$ : Equil. solubility of very large particles)

Coarsening rate  $\frac{d\bar{r}}{dt} \propto \frac{k}{\bar{r}^2}$



$D$  and  $X_e \sim \exp(-Q/RT)$   
 $\bar{r}$  rapidly increase with increasing temp. ⇒ CR ↑

(Ostwald Ripening)



: Concentration gradient in matrix → diffusion → small particle\_shrink/ large particle\_grow

### 3.3 Calculation of critical radius

1) Assumption: solid ~ incompressible (two phases were at the same pressure),

$$T_E \rightarrow T_E - \Delta T, \Delta G_P (2\sigma/r^*) = \Delta P$$

$$G^L = H^L - TS^L$$

$$G^S = H^S - TS^S$$

$$\Delta G_P = \Delta H - T \Delta S$$

$$\Delta G_P = 0 = \Delta H - T_E \Delta S$$

$$L : \Delta H = H^L - H^S$$

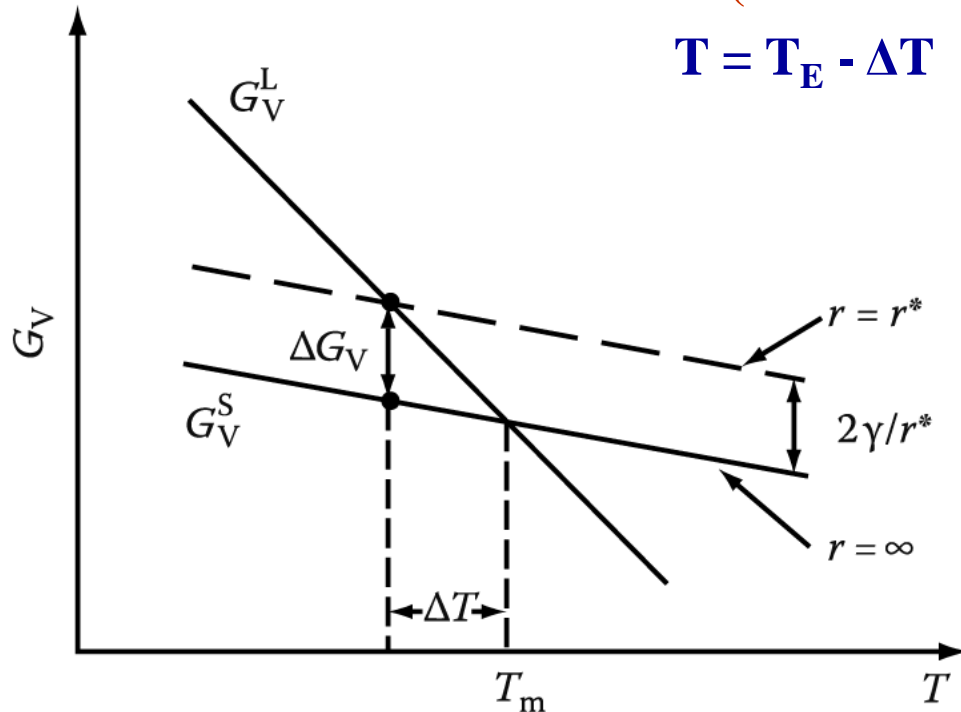
$$\Delta S = \Delta H / T_E = L / T_E$$

(Latent heat)

$$\Delta G_P = L - T(L/T_E) \approx (L\Delta T) / T_m$$

$$T = T_E - \Delta T$$

$$\Delta G_V = \Delta G_P = \frac{L\Delta T}{T_E}$$



**For incompressible solid,**

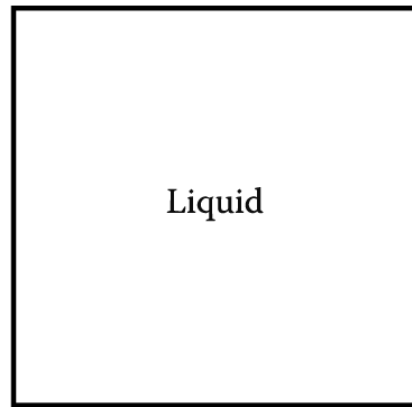
$$\frac{L\Delta T}{T_E} = \frac{2\sigma}{r^*}, \quad \text{or} \quad r^* = \frac{2\sigma T_E}{L\Delta T}$$

$\Delta H, \Delta S$  : independent of temperature

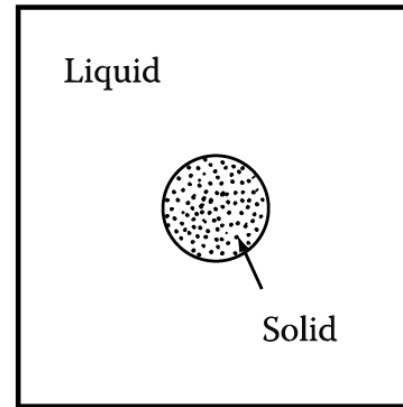
→ if the nucleation status is not incompressible,  $\Delta G_P \neq \Delta P$

( ex. Nucleation of gas or vapor in liquid )

## 2) Calculation of critical radius II



(a)  $G_1$



(b)  $G_2 = G_1 + \Delta G$

$$G_1 = (V_S + V_L)G_V^L$$

$$G_2 = V_S G_V^S + V_L G_V^L + A_{SL} \gamma_{SL}$$

$G_V^S, G_V^L$  : free energies per unit volume

$$\Delta G = G_2 - G_1 = -V_S (G_V^L - G_V^S) + A_{SL} \gamma_{SL}$$

for spherical nuclei (isotropic) of radius :  $r$

$$\Delta G_r = -\frac{4}{3} \pi r^3 \Delta G_V + 4\pi r^2 \gamma_{SL}$$

## 2) Calculation of critical radius II

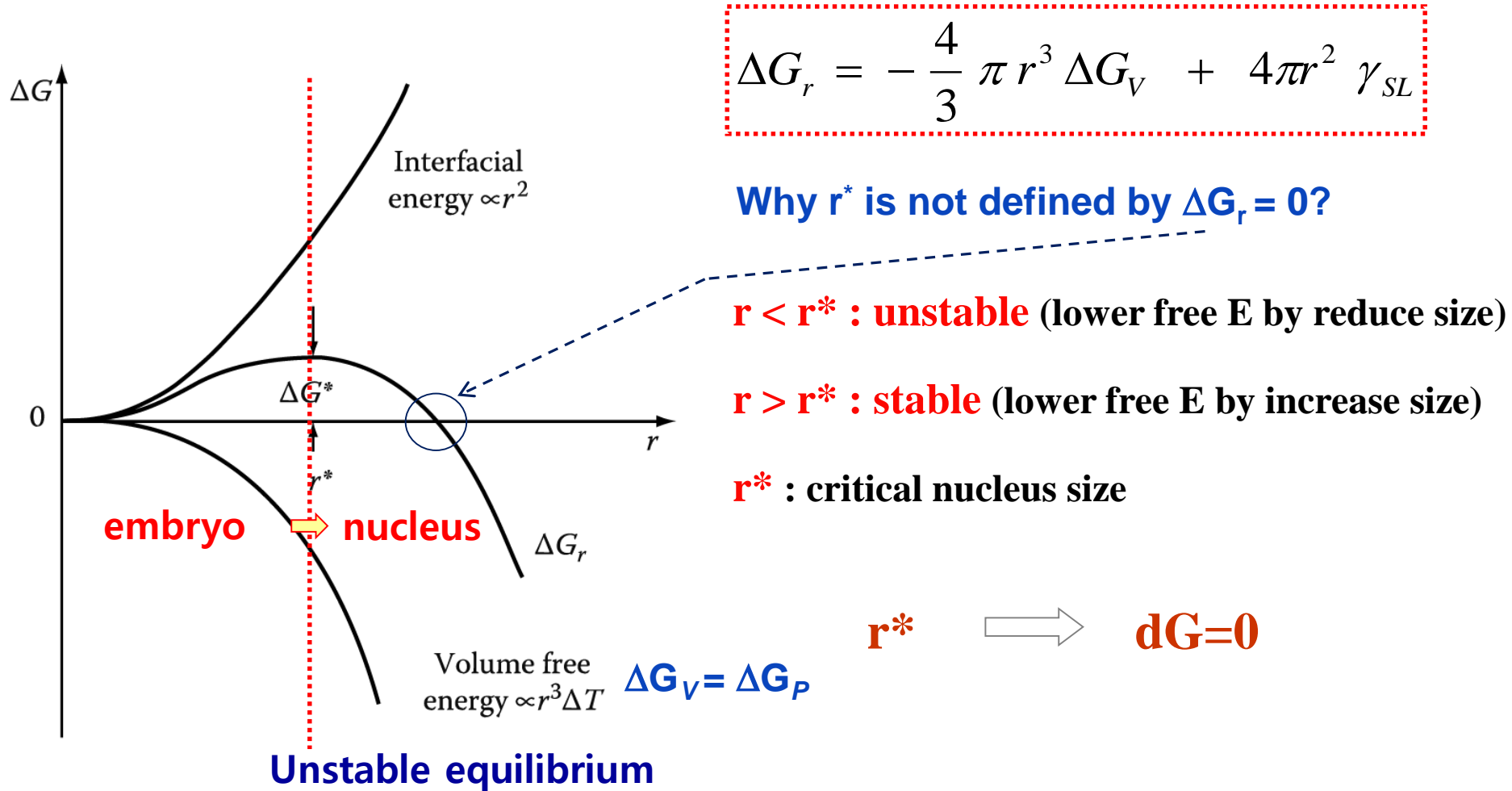


Fig. 4. 2 The free energy change associated with homogeneous nucleation of a sphere of radius  $r$ .

# Gibbs-Thompson Equation

$\Delta G$  of a spherical particle of radius,  $r$

$$\Delta G_{r(s)} = 4\pi r^2 \gamma$$

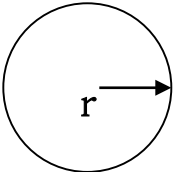
$\Delta G$  of a supersaturated solute in liquid in equilibrium with a particle of radius,  $r$

$$\Delta G_{r(l)} = \frac{4\pi r^3}{3} \times \Delta G_V$$

**Equil. condition for open system**

→  $\Delta\mu$  should be the same.

$$\Delta\mu = 8\pi r \gamma = 4\pi r^2 \Delta G_V$$



$$\frac{2\gamma V_m}{r} \text{ /mole or } \frac{2\gamma}{r} \text{ / per unit volume}$$

$$\Delta G_V = 2\gamma_{SL} / r^*$$

$r^*$ : in (unstable) equilibrium with surrounding liquid

$$r^* = \frac{2\gamma_{SL}}{\Delta G_V} \quad \Rightarrow \quad \Delta G^* = \frac{16\pi \gamma_{SL}^3}{3(\Delta G_V)^2} = \left( \frac{16\pi \gamma_{SL}^3 T_m^2}{3L_V^2} \right) \frac{1}{(\Delta T)^2}$$

$$\Delta G_r = -\frac{4}{3} \pi r^3 \Delta G_V + 4\pi r^2 \gamma_{SL}$$

$$\Delta G_V = \frac{L\Delta T}{T_m}$$



- Critical condition of Nucleation → Depends on the curvature of the crystal surface
- To calculate  $r^*$  under a given  $\Delta T$ :  $\sigma = \gamma_{SL}$  (Sol.-Liq. Interfacial E) measurement required

$$r^* = \frac{2\sigma T_E}{L\Delta T}$$

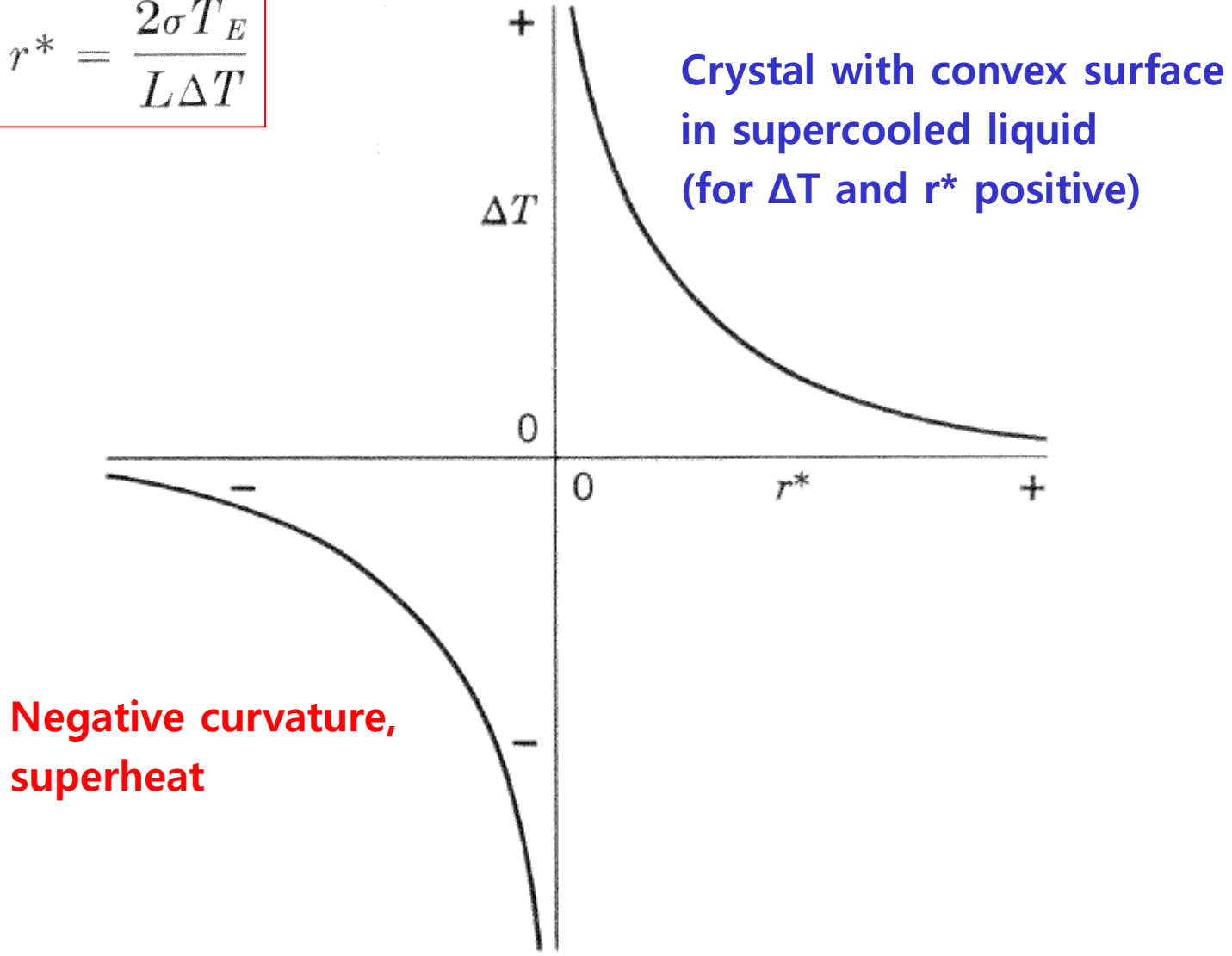
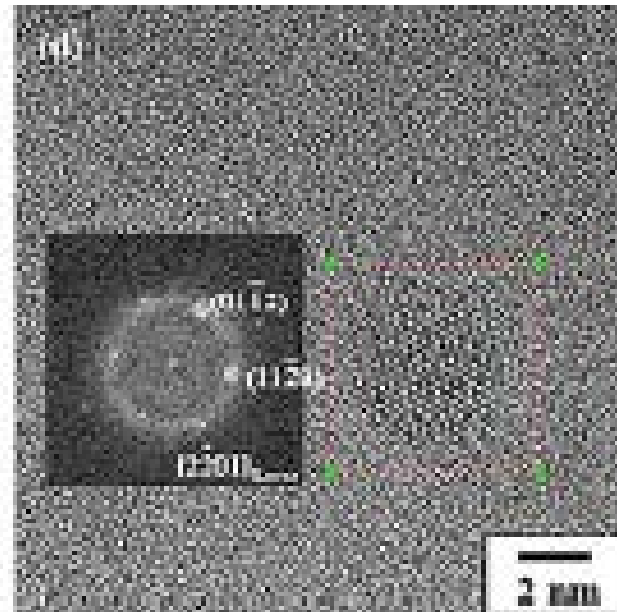
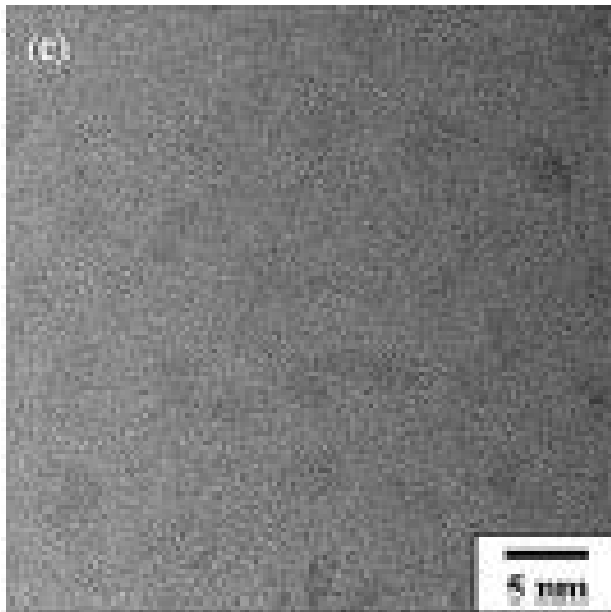
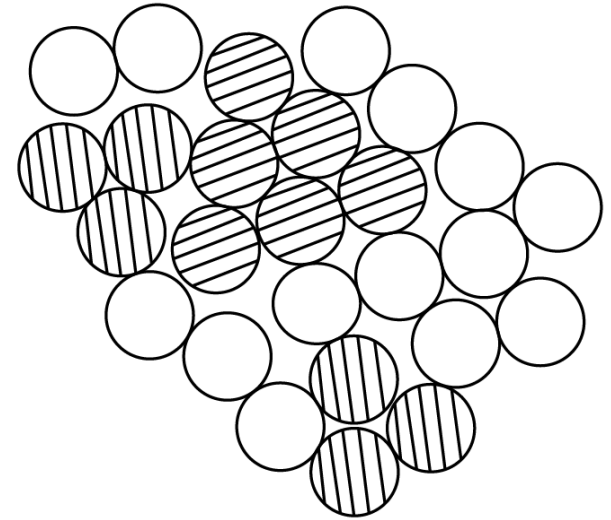


Fig. 3.3. Relationship between critical radius and supercooling.

# Formation of Atomic Cluster

At the  $T_m$ , the liquid phase has a volume 2-4% greater than the solid.

**Fig. 4.4** A two-dimensional representation of an instantaneous picture of the liquid structure. Many close-packed crystal-like clusters (shaded) are instantaneously formed.

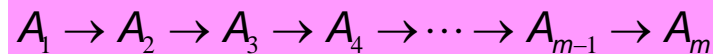


# Formation of Atomic Cluster

When the free energy of the atomic cluster with radius  $r$  is by

$$\Delta G_r = -\frac{4}{3}\pi r^3 \Delta G_V + 4\pi r^2 \gamma_{SL},$$

how many atomic clusters of **radius  $r$**  would exist in the presence of the total number of atoms,  $n_0$ ?



$n_2 = n_1 \exp\left(-\frac{\Delta G^{1 \rightarrow 2}}{kT}\right)$  Excess free E associated with the cluster of 1→2 atoms

$n_3 = n_2 \exp\left(-\frac{\Delta G^{2 \rightarrow 3}}{kT}\right)$

$n_4 = n_3 \exp\left(-\frac{\Delta G^{3 \rightarrow 4}}{kT}\right)$

$\vdots$   
 $n_m = n_{m-1} \exp\left(-\frac{\Delta G^{m-1 \rightarrow m}}{kT}\right)$

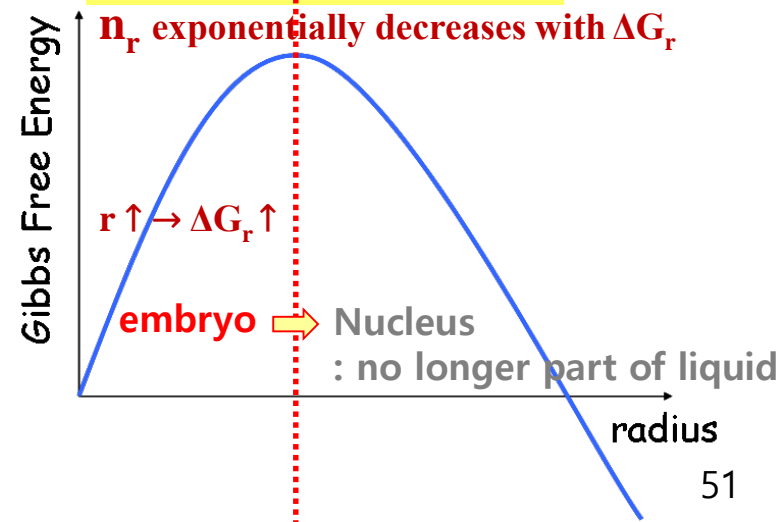
$n_m = n_1 \exp\left(-\frac{\Delta G^{1 \rightarrow 2} + \Delta G^{2 \rightarrow 3} + \dots + \Delta G^{m-1 \rightarrow m}}{kT}\right)$

$n_m = n_1 \exp\left(-\frac{\Delta G^{1 \rightarrow m}}{kT}\right)$

# of spherical clusters with radius  $r$

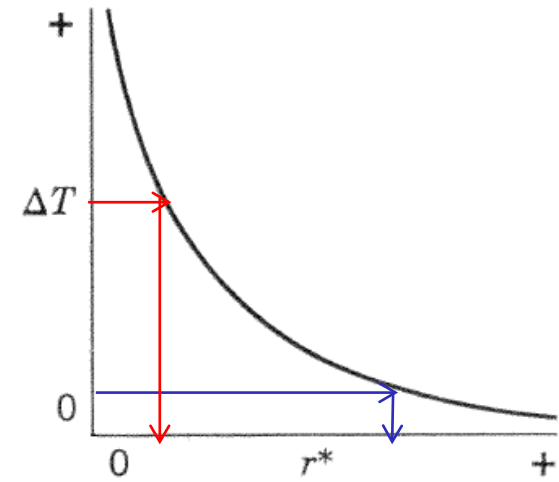
$n_r = n_0 \exp\left(-\frac{\Delta G_r}{kT}\right)$

# of cluster of radius  $r$

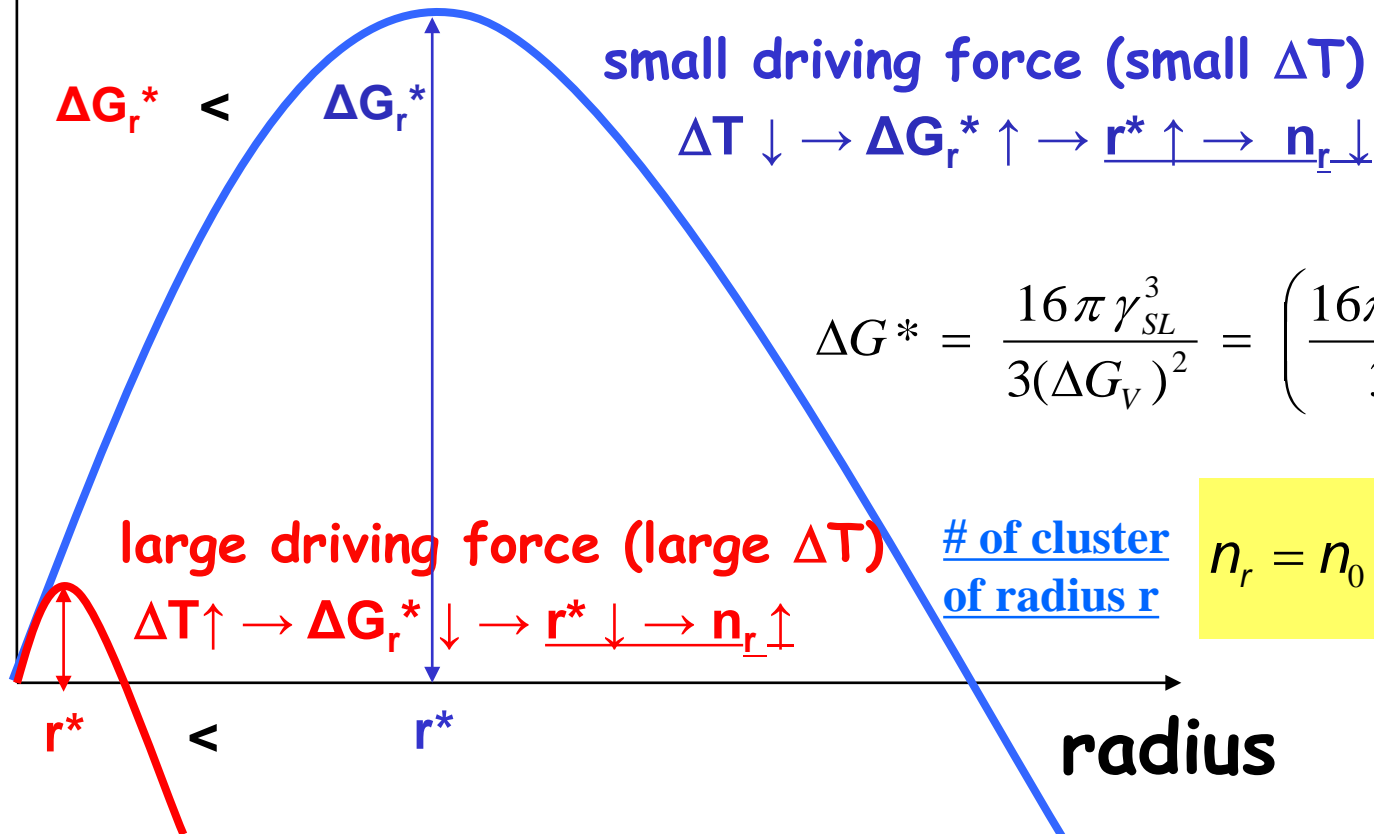


# Formation of Atomic Cluster

Compare the nucleation curves between small and large driving forces.



Gibbs Free Energy



$$\Delta G^* = \frac{16\pi\gamma_{SL}^3}{3(\Delta G_V)^2} = \left( \frac{16\pi\gamma_{SL}^3 T_m^2}{3L_V^2} \right) \frac{1}{(\Delta T)^2}$$

# of cluster of radius r

$$n_r = n_0 \exp\left(-\frac{\Delta G_r}{kT}\right)$$

# Formation of Atomic Cluster

$n_0$  : total # of atoms.

$\Delta G_r$  : excess free energy associated with the cluster

$k$  : Boltzmann's constant

# of cluster of radius  $r$  per unit volume

$$n_r = n_0 \exp\left(-\frac{\Delta G_r}{kT}\right)$$

-  $\Delta G_r \neq 0 \rightarrow n_r/n \neq 0$  (always cluster with a specific size)

$\rightarrow$  Key to nucleation : relationship btw  $r_{\max}$  and  $r^*$

- holds for  $T > T_m$  /  $T < T_m$  and  $r \leq r^*$

Apply for all  $r$  /  $r \leq r^*$

( $\because r > r^*$ : no longer part of the liquid)

-  $n_r$  exponentially decreases with  $\Delta G_r$

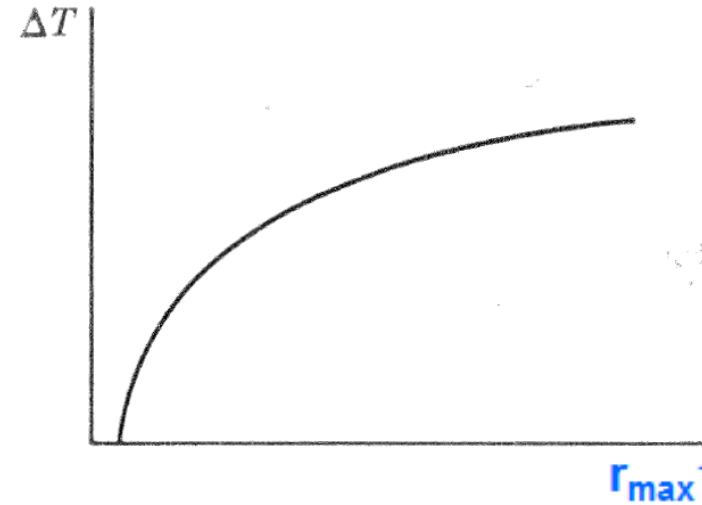


Fig. 3.5. Radius of largest embryo as a function of supercooling.

**Ex. 1 mm<sup>3</sup> of copper at its melting point ( $n_0$ :  $10^{20}$  atoms)**

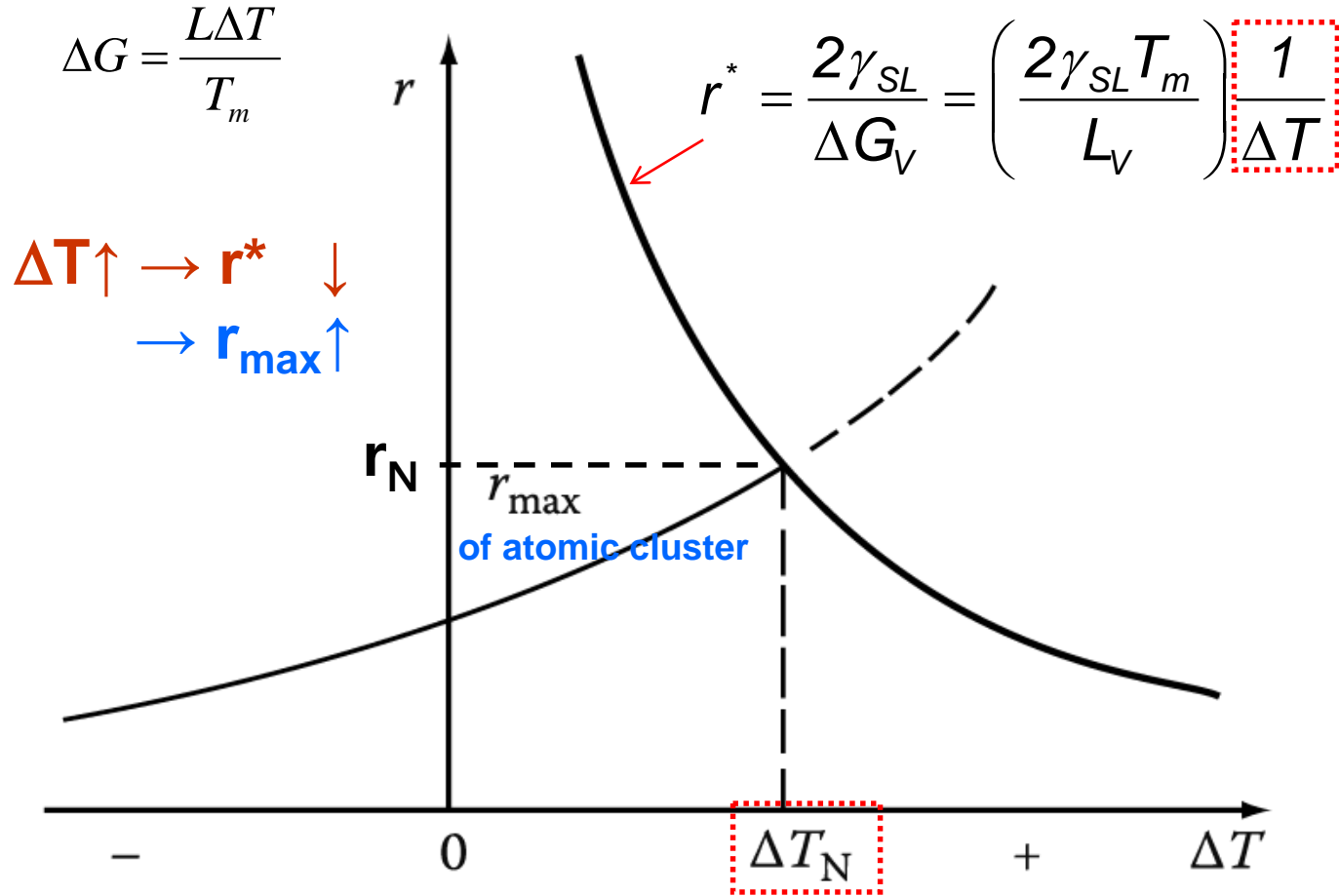
$r \downarrow \rightarrow n_r \uparrow \rightarrow \sim 10^{14}$  clusters of 0.3 nm radius (i.e.  $\sim 10$  atoms)

$r \uparrow \rightarrow n_r \downarrow \rightarrow \sim 10$  clusters of 0.6 nm radius (i.e.  $\sim 60$  atoms)

$\rightarrow$  effectively a maximum cluster size,  $\sim 100$  atoms

$\sim 10^{-8}$  clusters mm<sup>-3</sup> or 1 cluster in  $\sim 10^7$  mm<sup>3</sup>

# The creation of a critical nucleus ~ thermally activated process



$\Delta T_N$  is **the critical undercooling** for homogeneous nucleation.

The variation of  $r^*$  and  $r_{\max}$  with undercooling  $\Delta T$

→ The condition for nucleation:

**The number of clusters with  $r^*$  at  $T < \Delta T_N$  is negligible.**

## 2) The homogeneous nucleation rate - kinetics

How fast solid nuclei will appear in the liquid at a given undercooling?

$n$  : atoms/unit volume

$n_i^*$  : # of clusters with size of  $r^*$  ( critical size )

$$n_i^* = n \exp\left(-\frac{\Delta G^*}{kT}\right) \text{ clusters / m}^3$$

$$\Delta G^* = 16\pi\sigma^3 / (\Delta G_P)^2$$

Excess free E of critical nucleus

The addition of one more atom to each of these clusters will convert them into stable nuclei.

Homogeneous nucleation rate  
(small embryos  $\rightarrow r^*$ )

$$N_{\text{hom}} = I \cdot ZS^* n_i^*$$

nuclei / m<sup>3</sup>·s

Net rate at which atoms travel  
across the interface btw liquid  
and embryo

Surface area of  
Critical nucleus

Equilibrium # of  
Critical nuclei

## 2) The homogeneous nucleation rate - kinetics

$$I = K_v \exp \left\{ - \left[ (\Delta G^* + \Delta G_A) / kT \right] \right\}$$

$$K_v = n^* (a_\sigma / 9\pi kT)^{1/2} n (kT/h)$$

a: correction factor of nucleus shape (Not necessarily spherical)

n\*: # of surface atoms for critical nucleus

n = # of atoms per unit volume for liquid

**Assumption:** “equilibrium distribution of the embryo size at all times” (ideal condition)

Vapor → liquid drop : OK but liquid → Solid : X due to low mobility

$$I = \frac{nkT}{h} \exp \left( - \frac{G_A}{kT} \right) \exp \left( - \frac{16\pi\sigma_{SL}^3 T_E^2}{3L^2 (\Delta T)^2 kT} \right)$$

→ Until  $\Delta T$  reaches, the critical value  $I$  is very small.

But  $\Delta T$  increases rapidly when critical value is reached



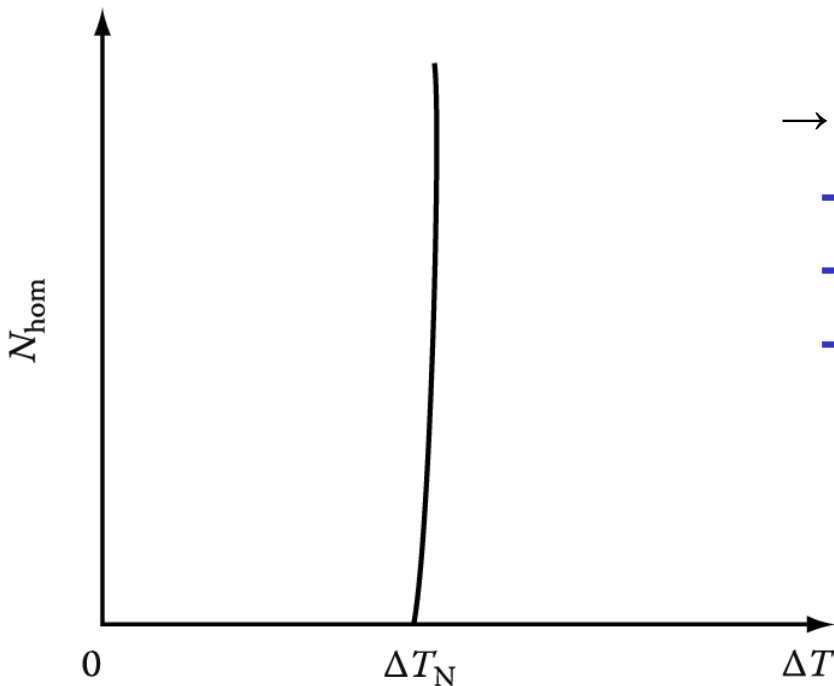
# The homogeneous nucleation rate - kinetics

$$I = \frac{nkT}{h} \exp\left(-\frac{G_A}{kT}\right) \exp\left(-\frac{16\pi\sigma_{SL}^3 T_E^2}{3L^2(\Delta T)^2 kT}\right)$$

: insensitive to Temp.

How do we define nucleation temperature,  $\Delta T_N$  ?

$$N_{\text{hom}} \sim \frac{1}{\Delta T^2}$$



→ **critical value for detectable nucleation**

- **critical supersaturation ratio**
- **critical driving force**
- **critical supercooling**

→ **for most metals,  $\Delta T_N \sim 0.2 T_m$  (i.e.  $\sim 200\text{K}$ )**

The homogeneous nucleation rate as a function of undercooling  $\Delta T$ .  $\Delta T_N$  is **the critical undercooling** for homogeneous nucleation.

\* **Comparison between experiment and theory**

**Most metal  $\Delta T_N < \text{several K}$**

**but Turnbull and his coworker  $\Delta T_N \rightarrow \text{larger}$  (~several hundreds K) by formation of large number of very small drops**

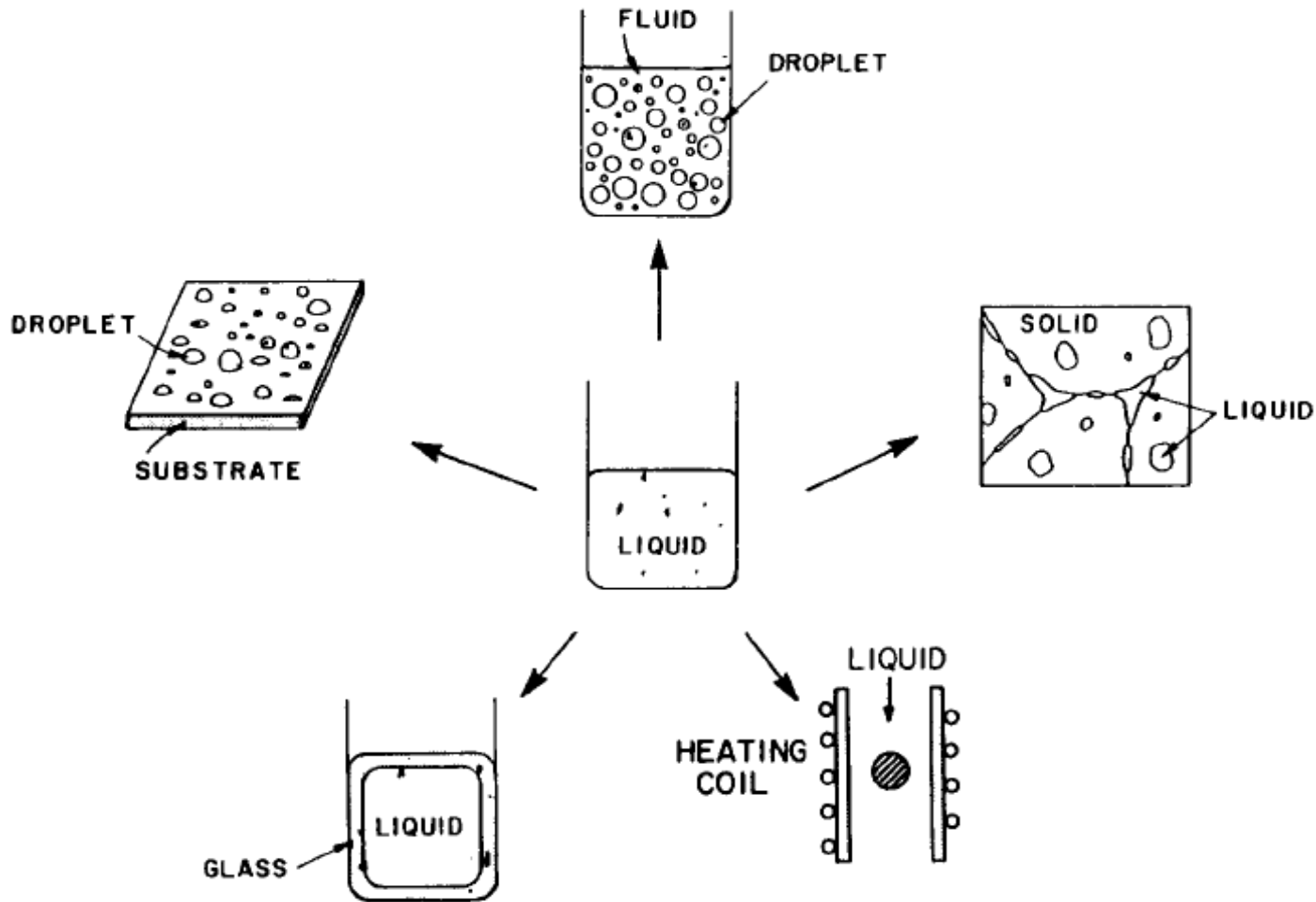
**Table 3.1. Relationship between Maximum Supercooling, Solid-Liquid Interfacial Energy and Heat of Fusion<sup>a</sup>**

Metal	Interfacial Energy $\sigma$ (ergs/cm <sup>2</sup> )	$\sigma_g$ (cal/mole)	$\sigma_g/L$	$\Delta T_{MAX}$ (deg)
Mercury	24.4	296	0.53	77
Gallium	55.9	581	0.44	76
Tin	54.5	720	0.42	118
Bismuth	54.4	825	0.33	90
Lead	33.3	479	0.39	80
Antimony	101	1430	0.30	135
Germanium	181	2120	0.35	227
Silver	126	1240	0.46	227
Gold	132	1320	0.44	230
Copper	177	1360	0.44	236
Manganese	206	1660	0.48	308
Nickel	255	1860	0.44	319
Cobalt	234	1800	0.49	330
Iron	204	1580	0.45	295
Palladium	209	1850	0.45	332
Platinum	240	2140	0.45	370

<sup>a</sup> Data from D. Turnbull, *J. Appl. Phys.*, **21**, 1022 (1950) and Ref. 3.

# How to Obtain Extensive Undercooling

John H. PEREPEZKO, MSE, 65 (1984) 125-135



By dispersing a liquid into a large number of small droplets within a suitable medium, the catalytic effects of active nucleants may be restricted to a small fraction of the droplets so that many droplets will exhibit extensive undercooling. 59

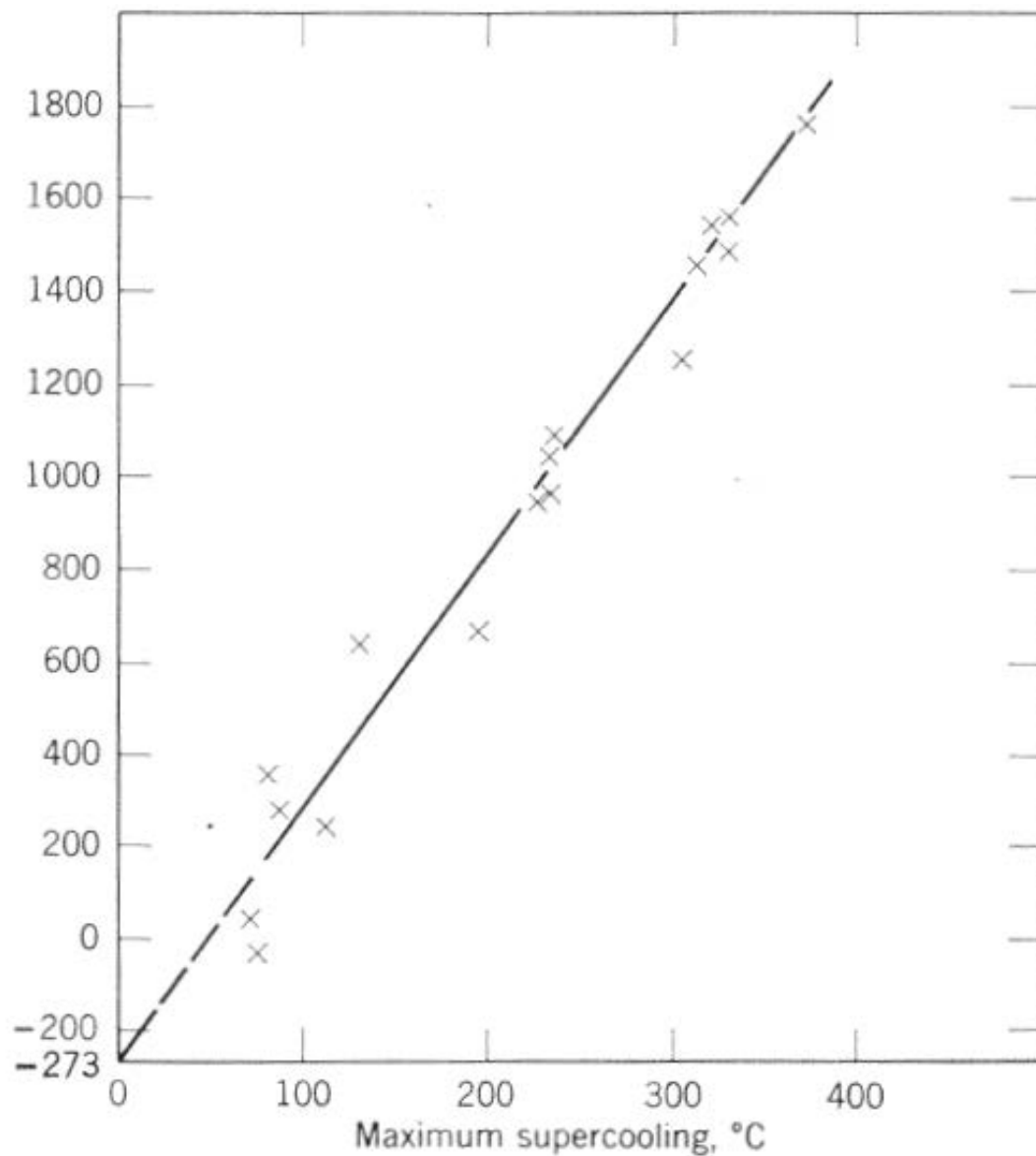


Fig. 3.7. Maximum supercooling as a function of melting point. (From *Thermodynamics in Physical Metallurgy*, American Society for Metals, Cleveland, 1911, p. 11.)

# Maximum undercooling vs. Melting temperature

